

FIG.1A

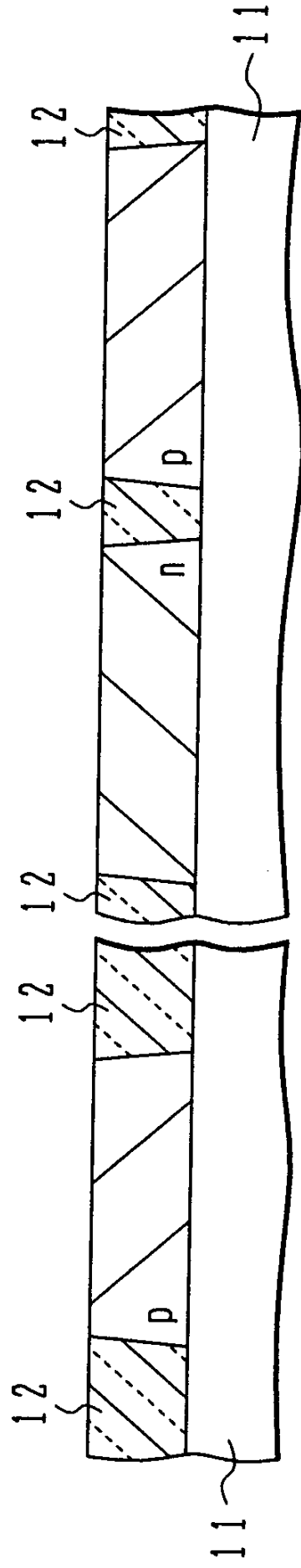


FIG.1B

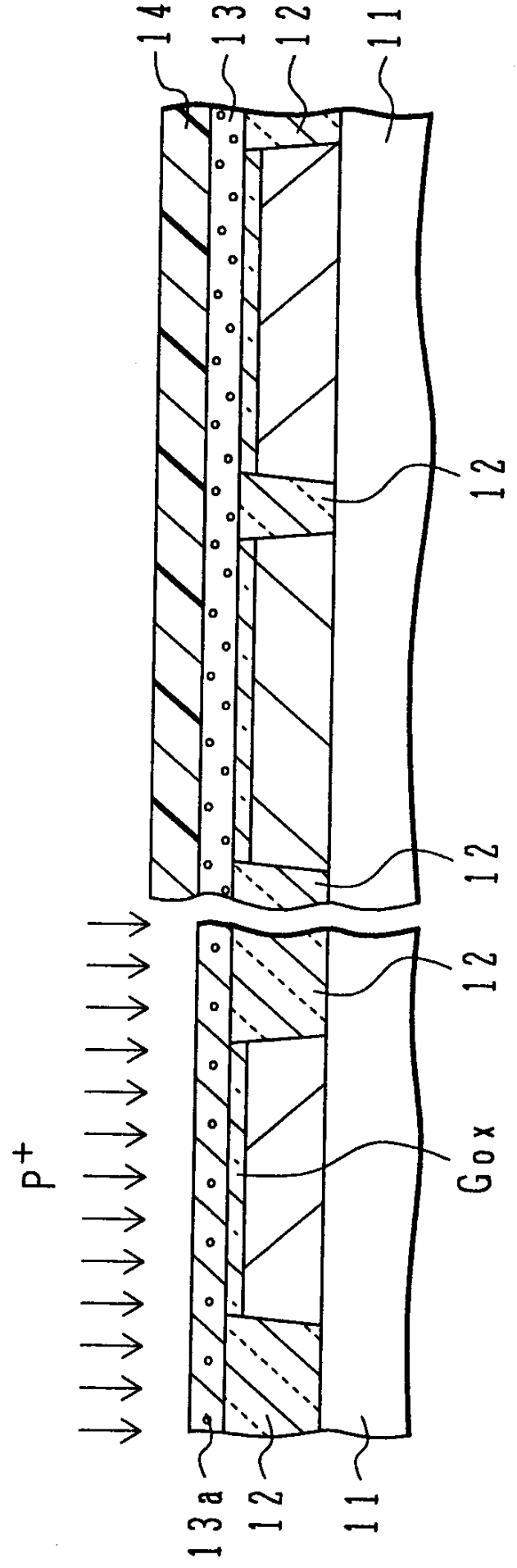


FIG. 2A

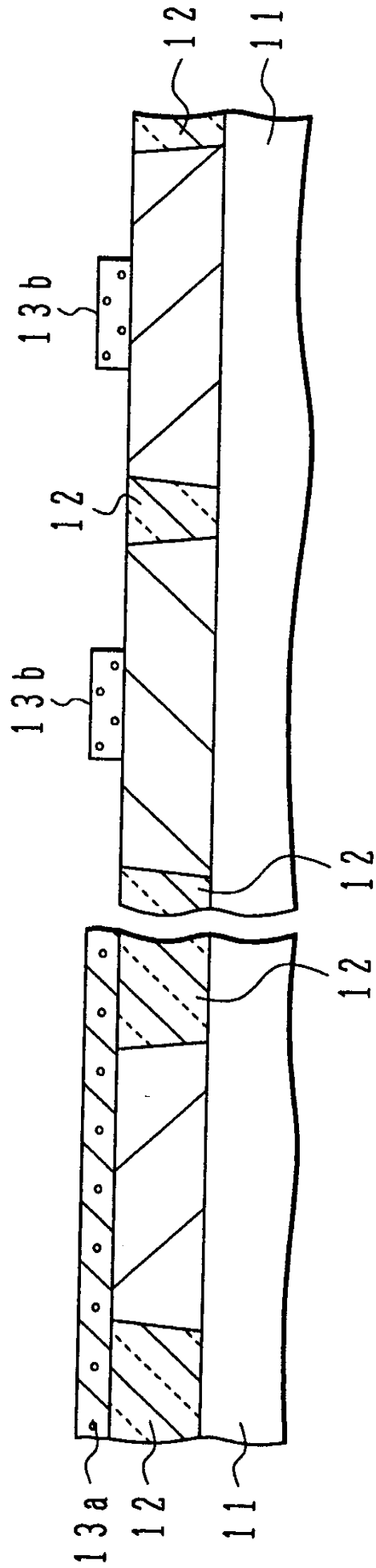
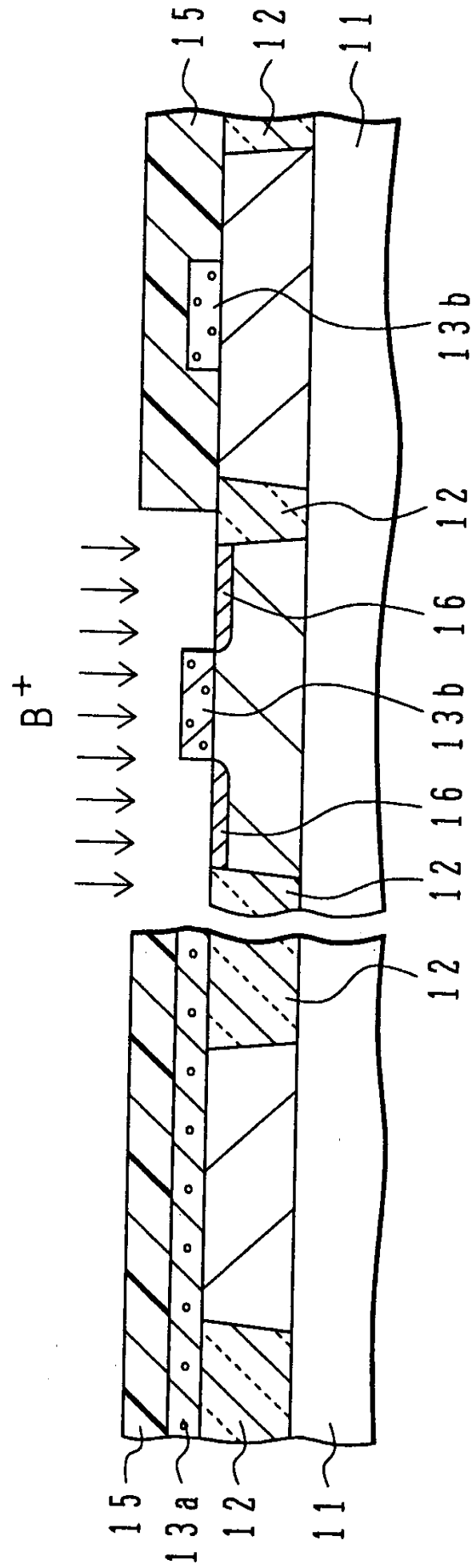
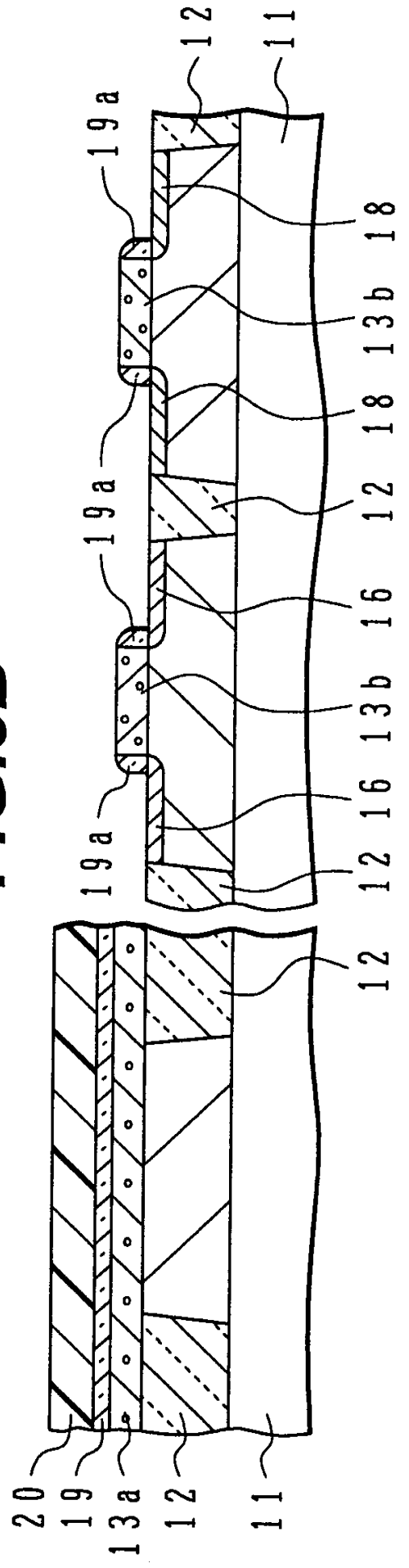


FIG. 2B





[illegible]

FIG.8

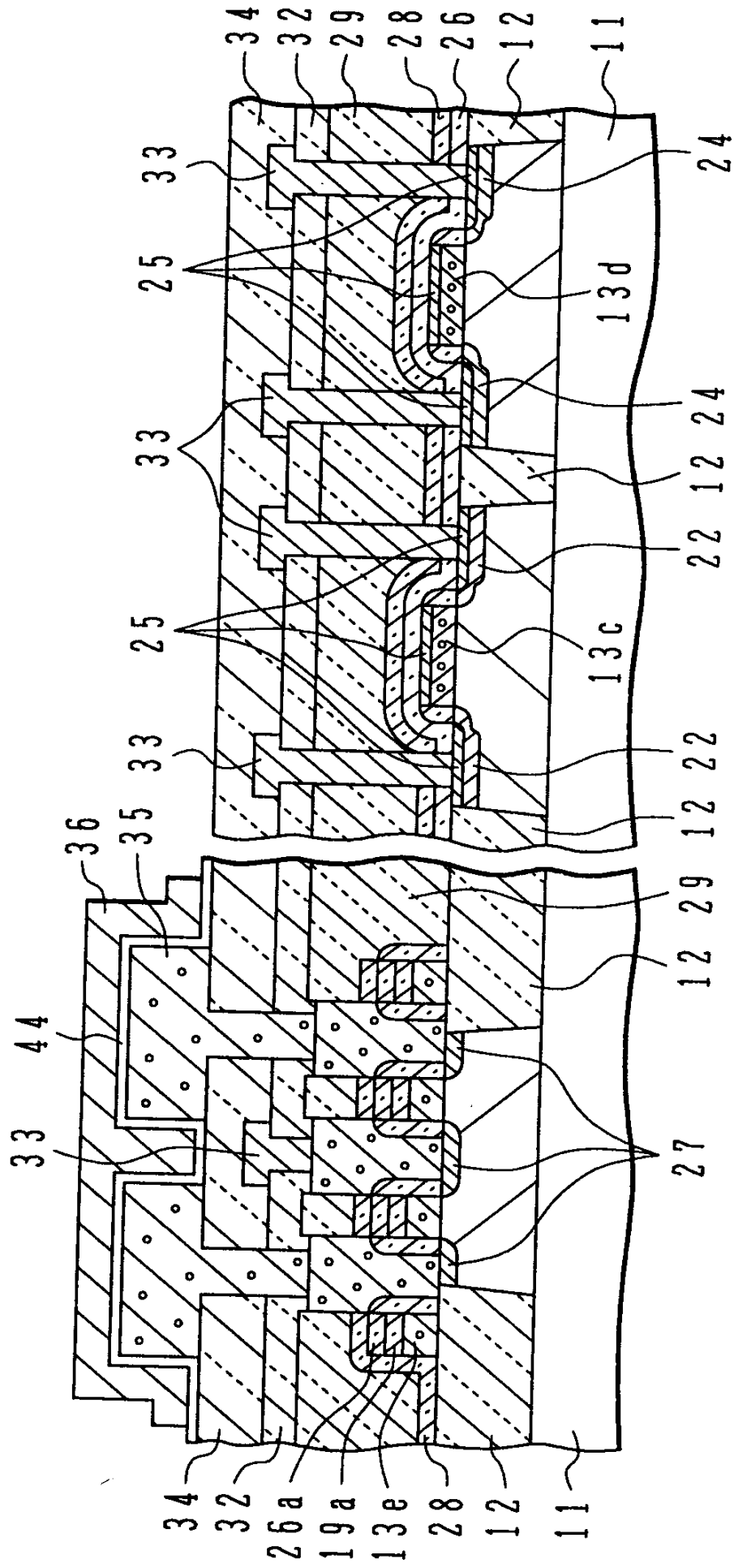


FIG.9

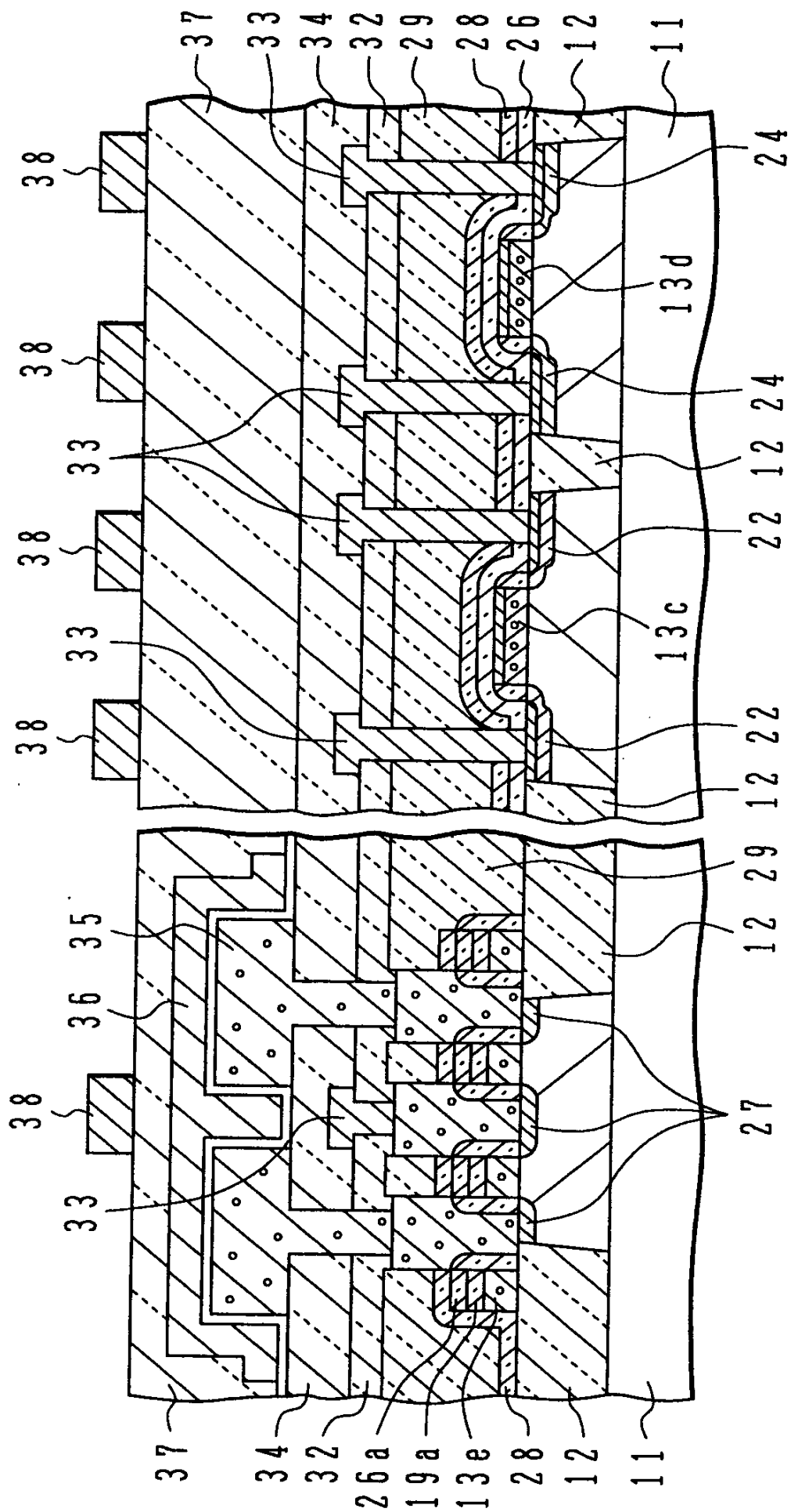


FIG.10

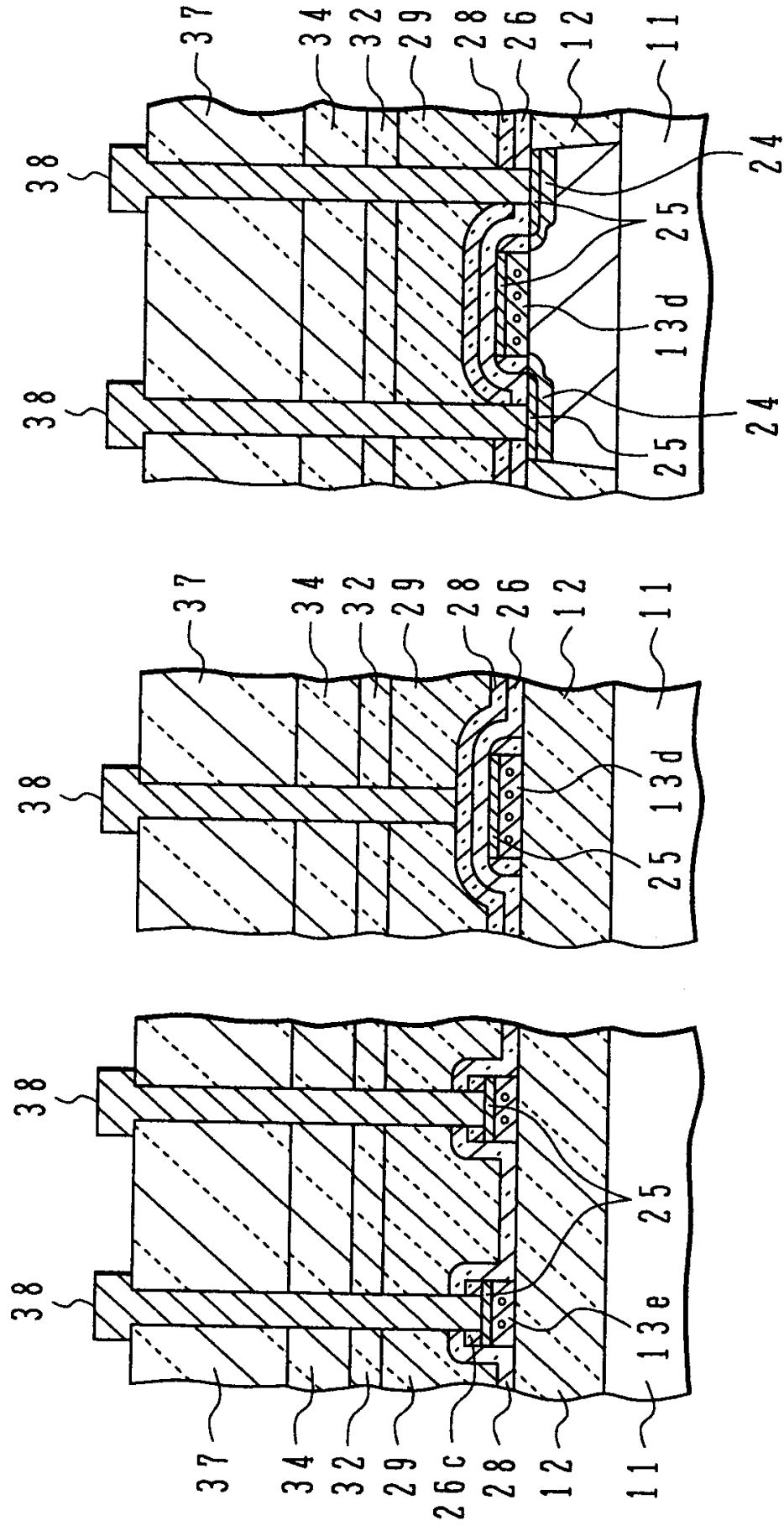


FIG. 11

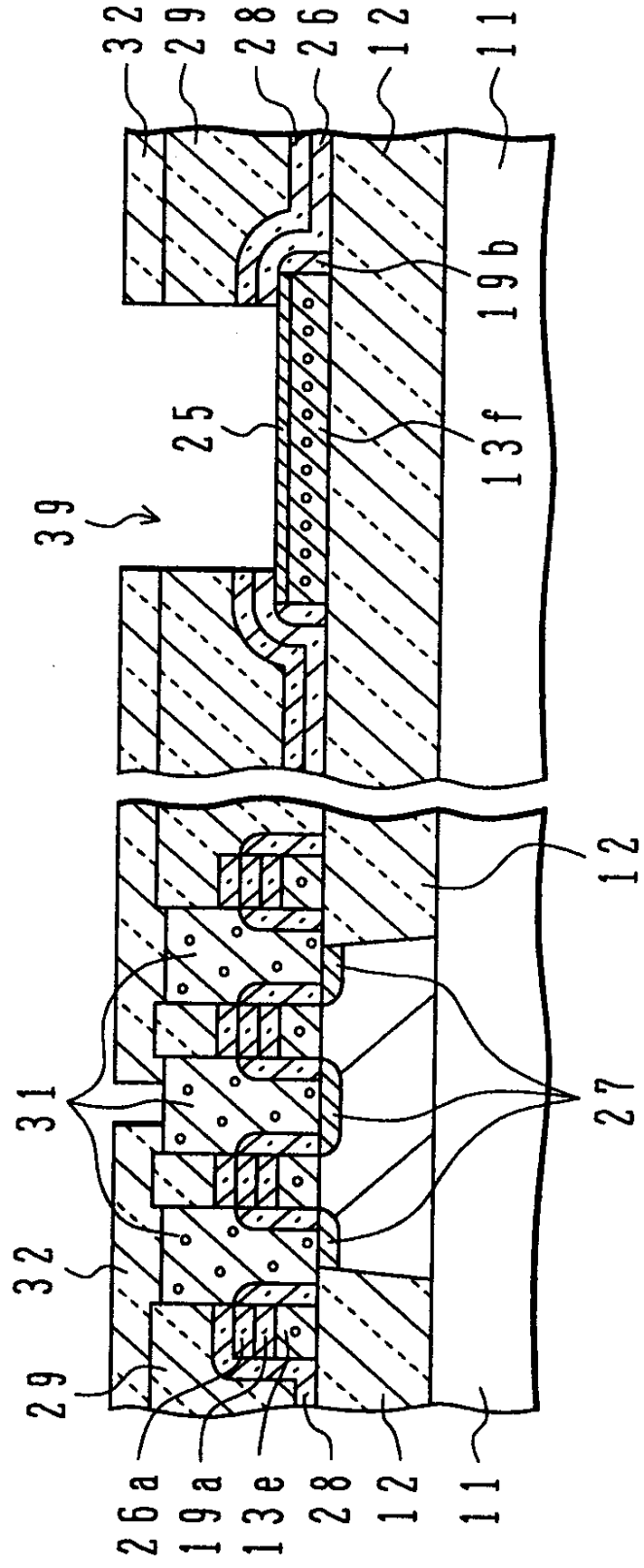


FIG.14A

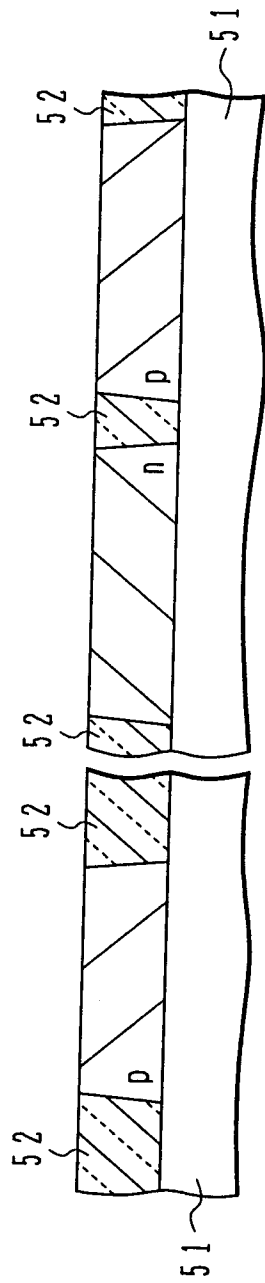


FIG.14B

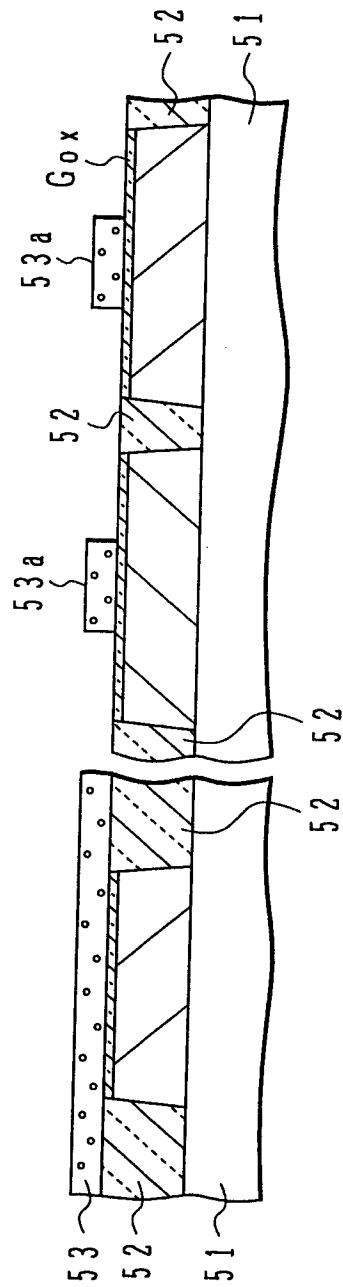


FIG. 15A

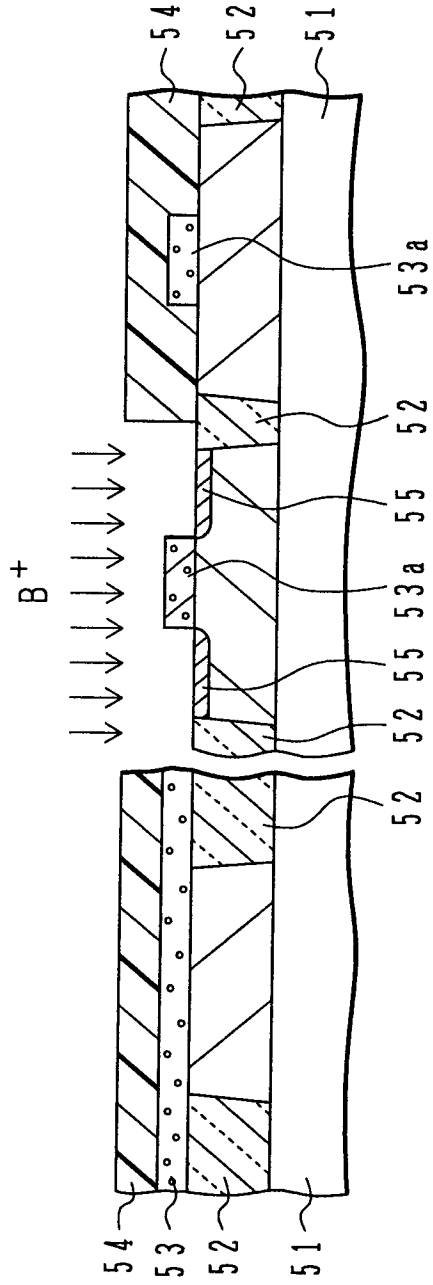


FIG. 15B

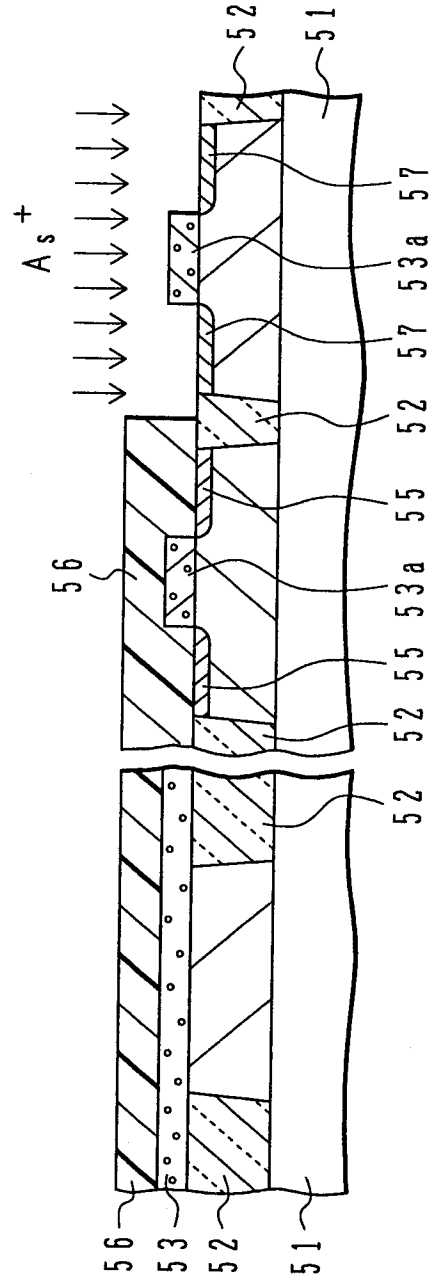


FIG. 16A

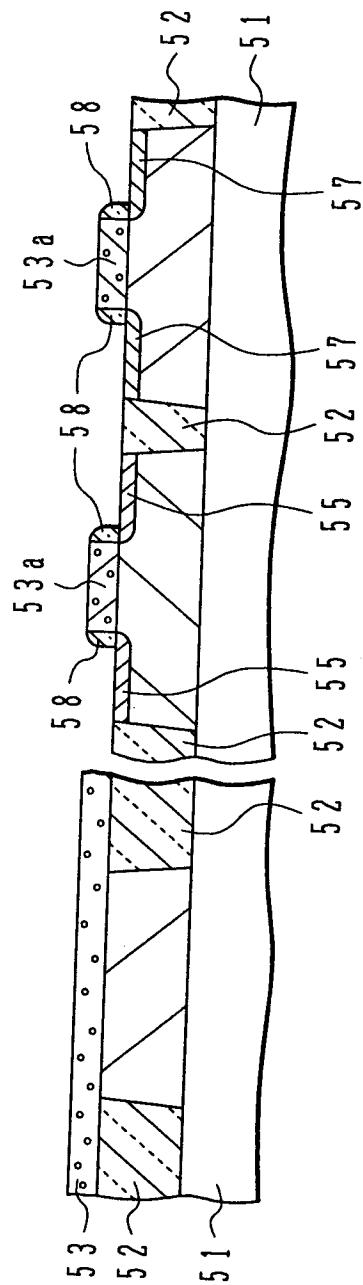


FIG. 16B

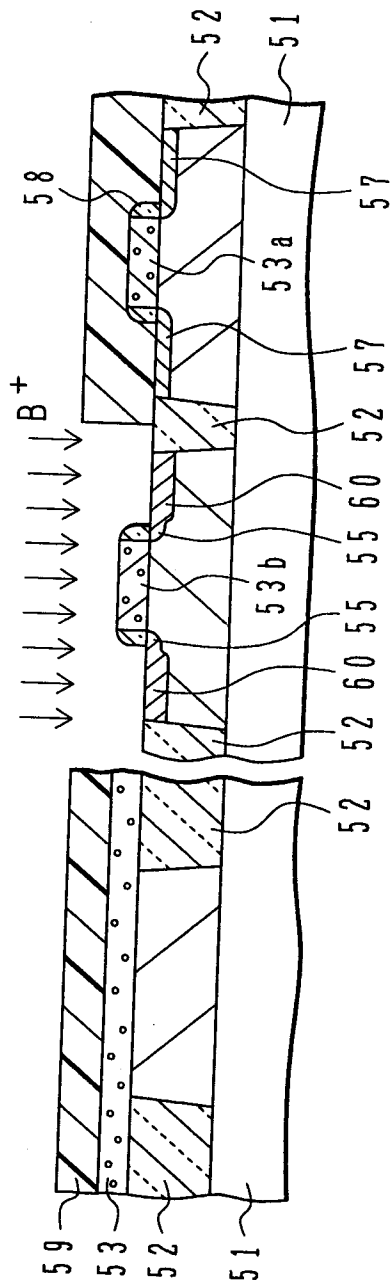


FIG.18A

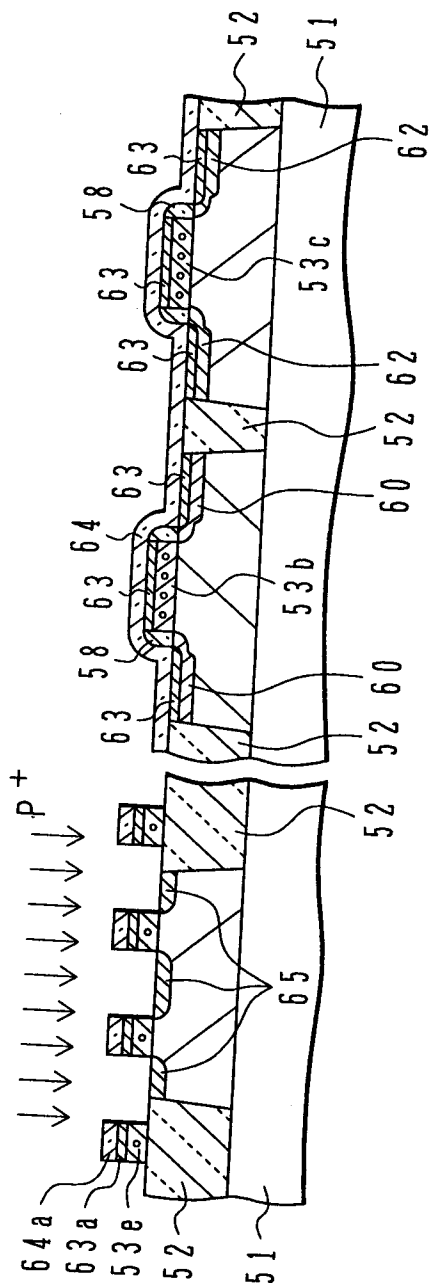


FIG.18B

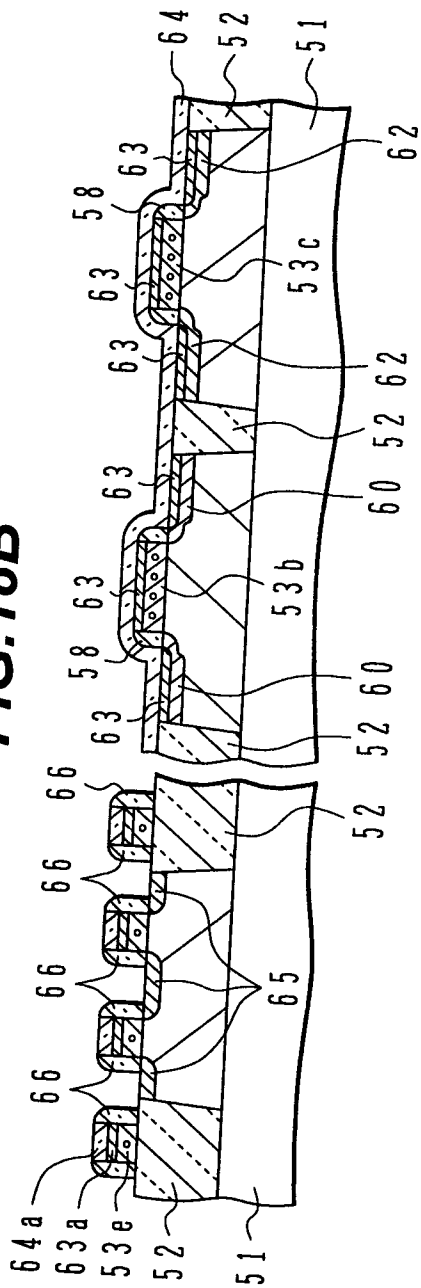


FIG.19

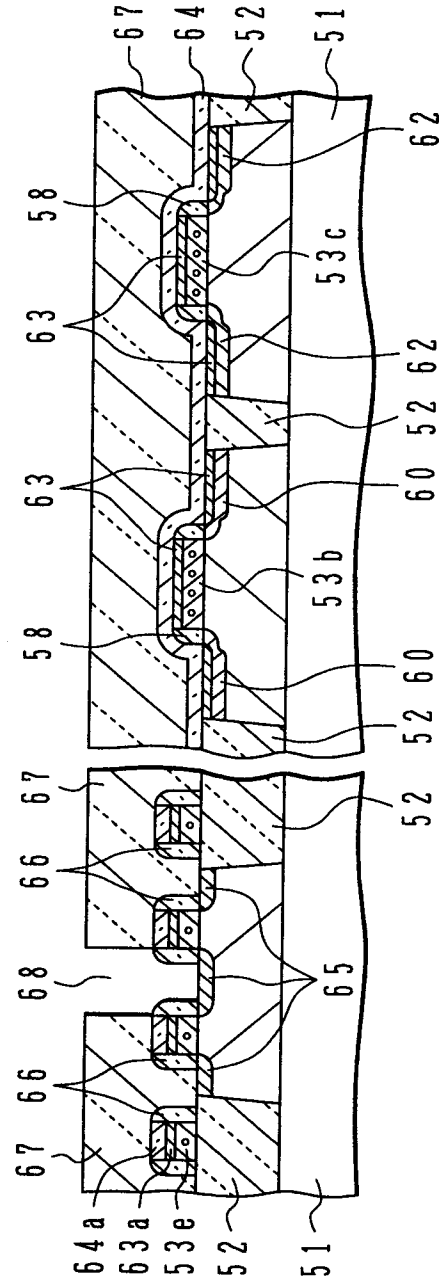


FIG. 20

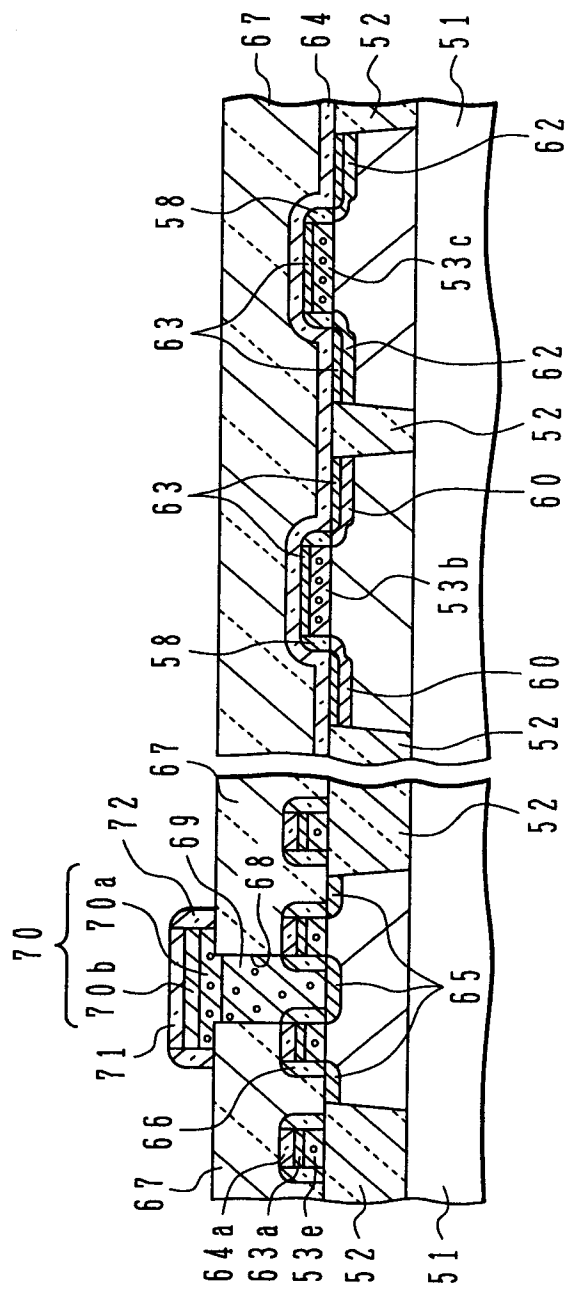
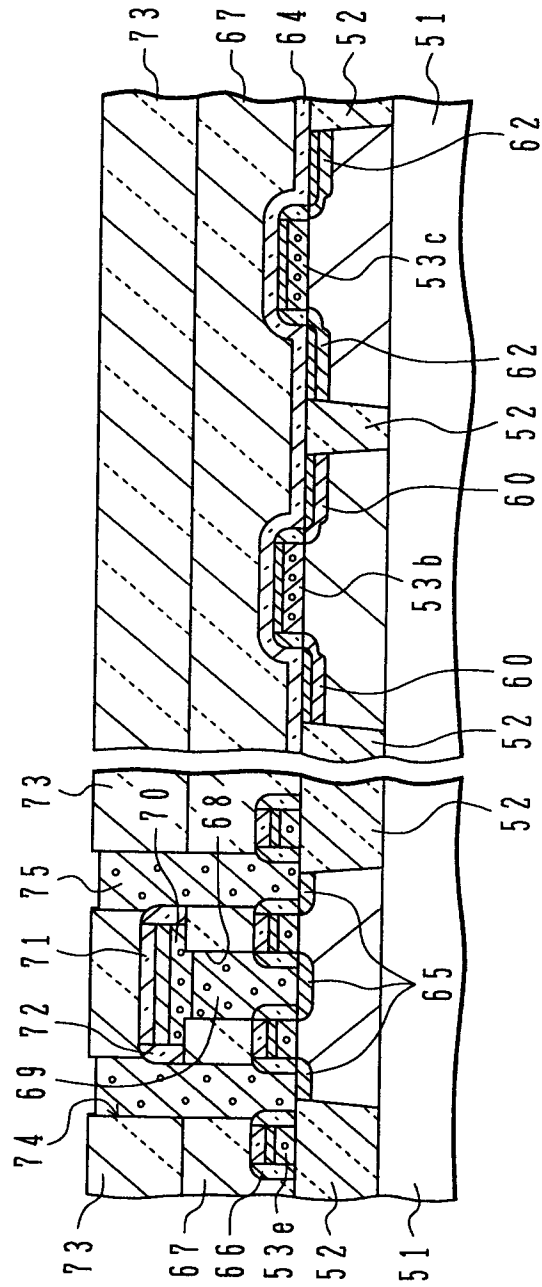


FIG. 21



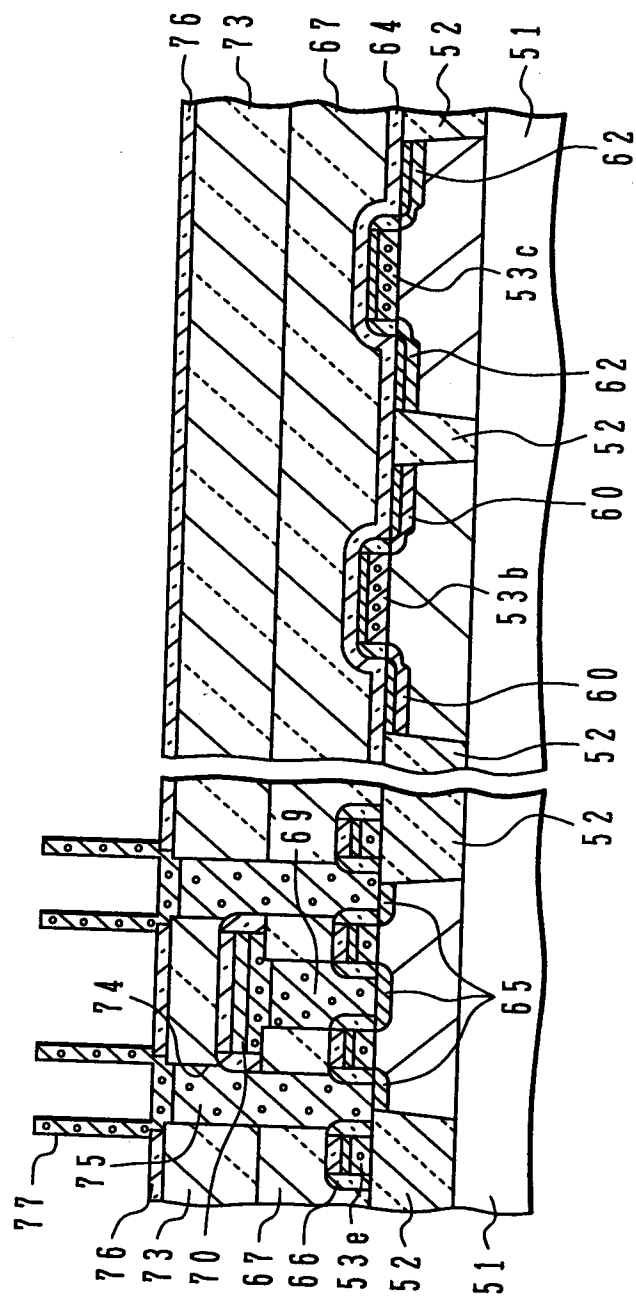


FIG. 23

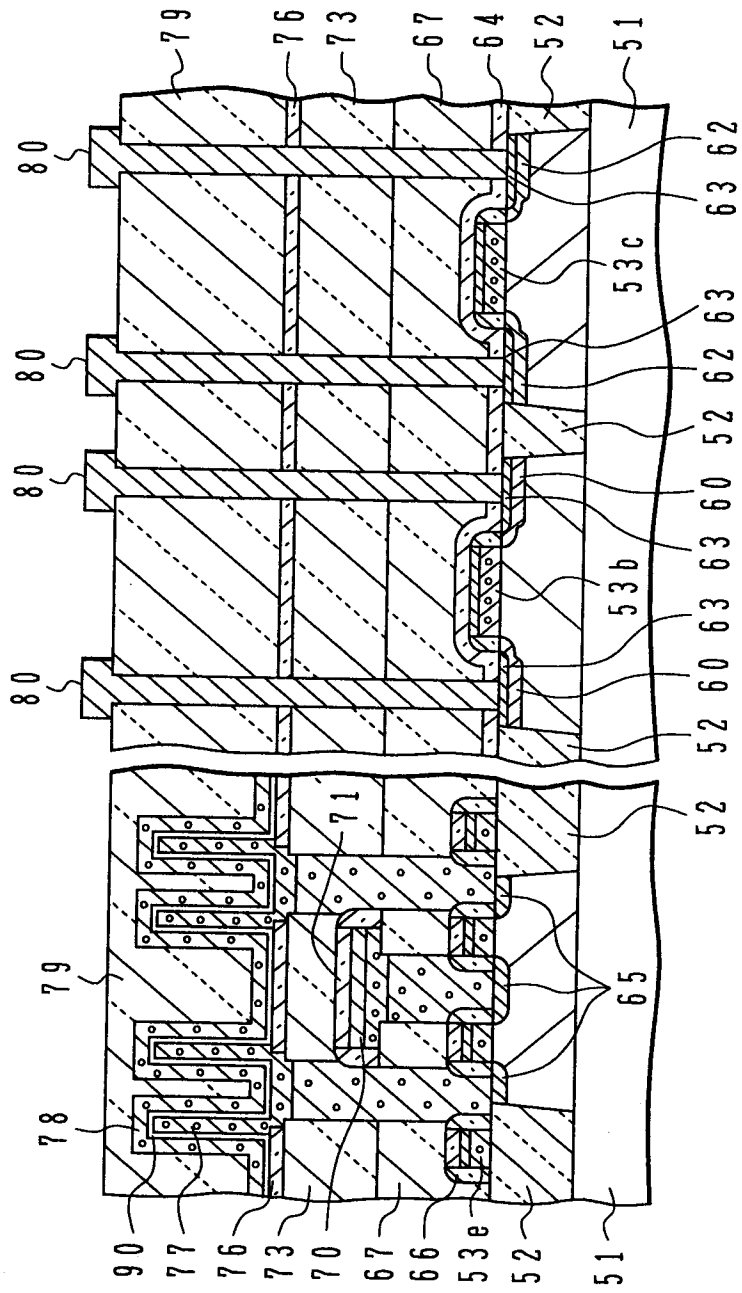


FIG.24

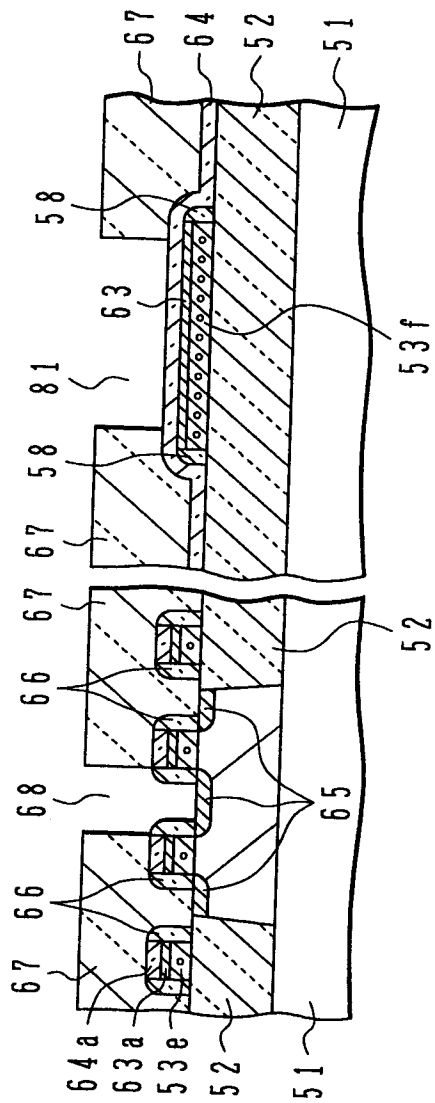


FIG.25

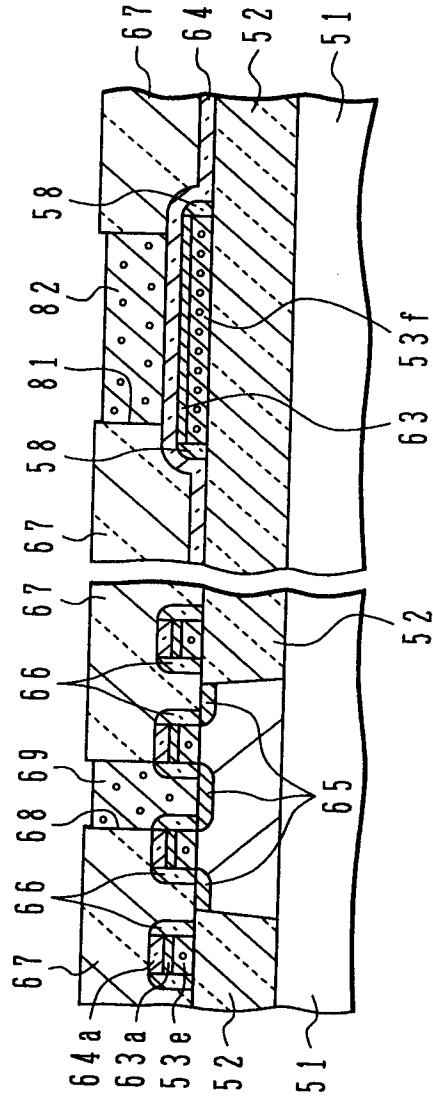


FIG.26

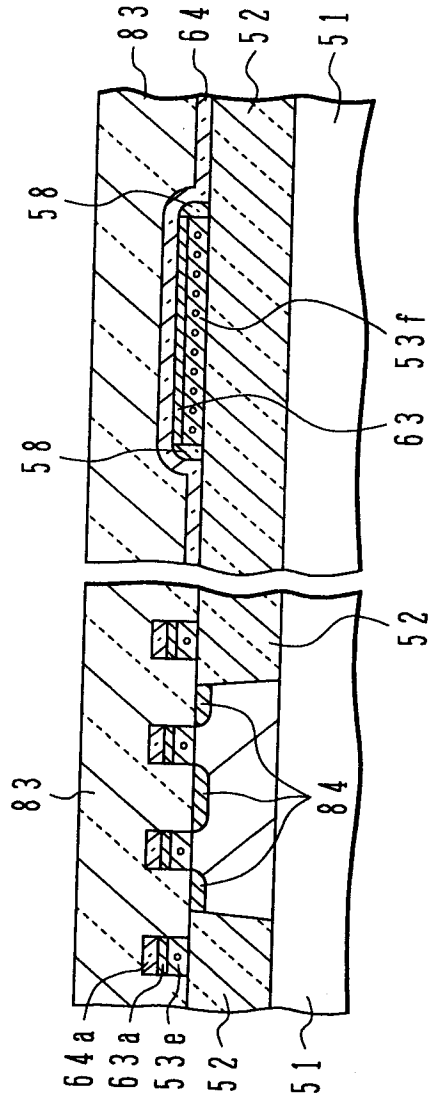


FIG.27

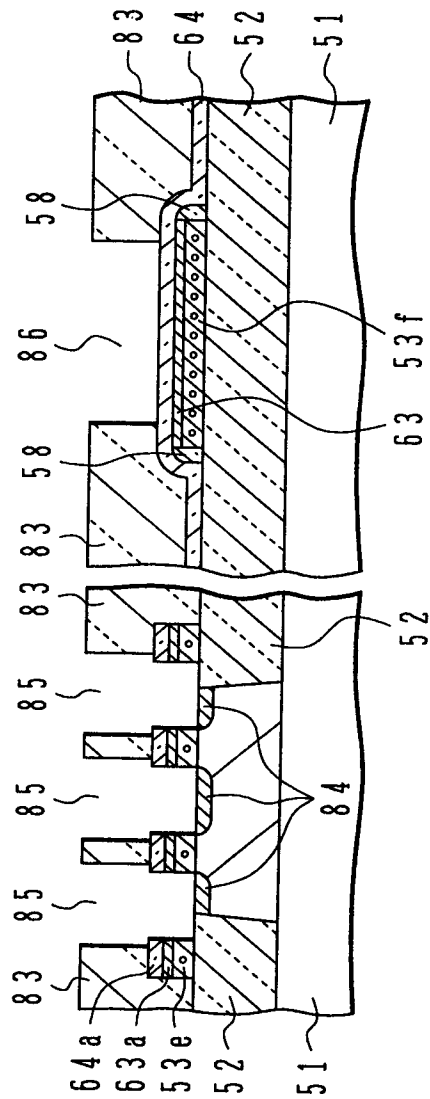


FIG.28

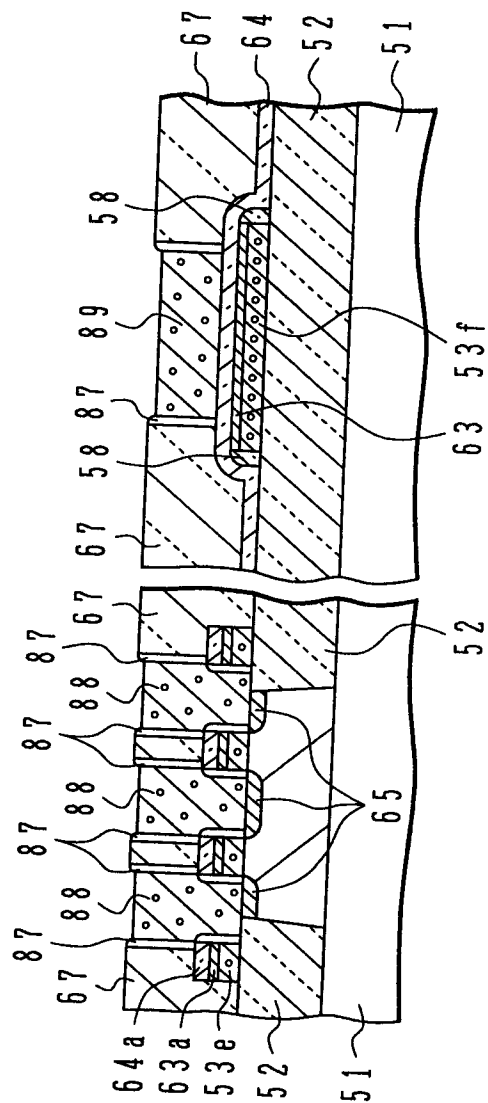


FIG. 29A

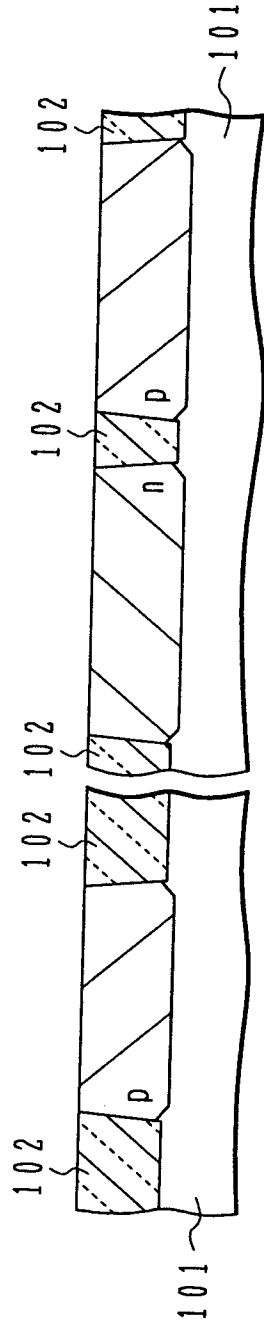


FIG. 29B

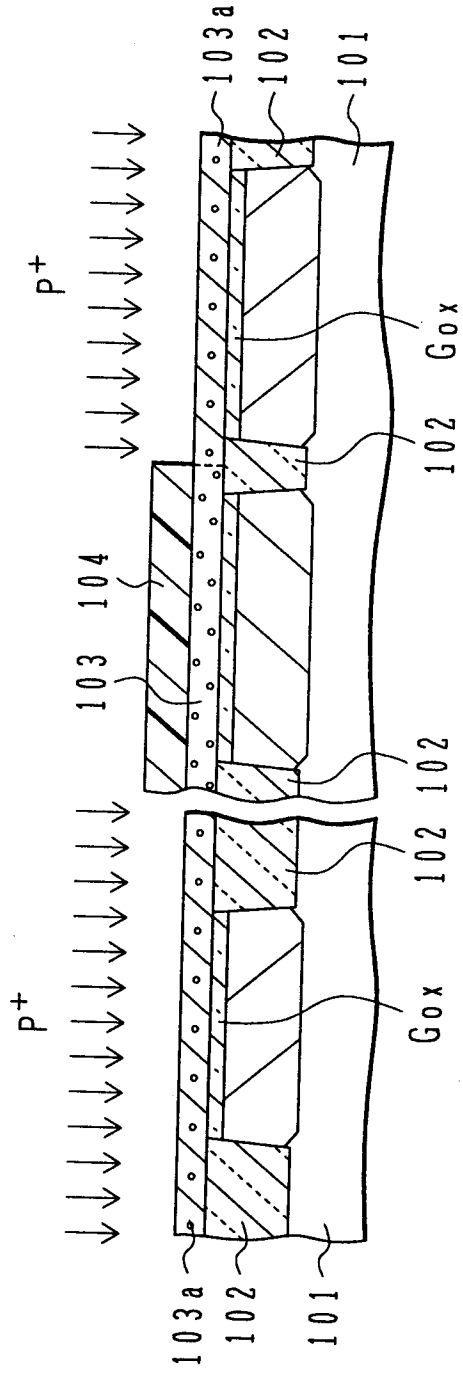


FIG.30A

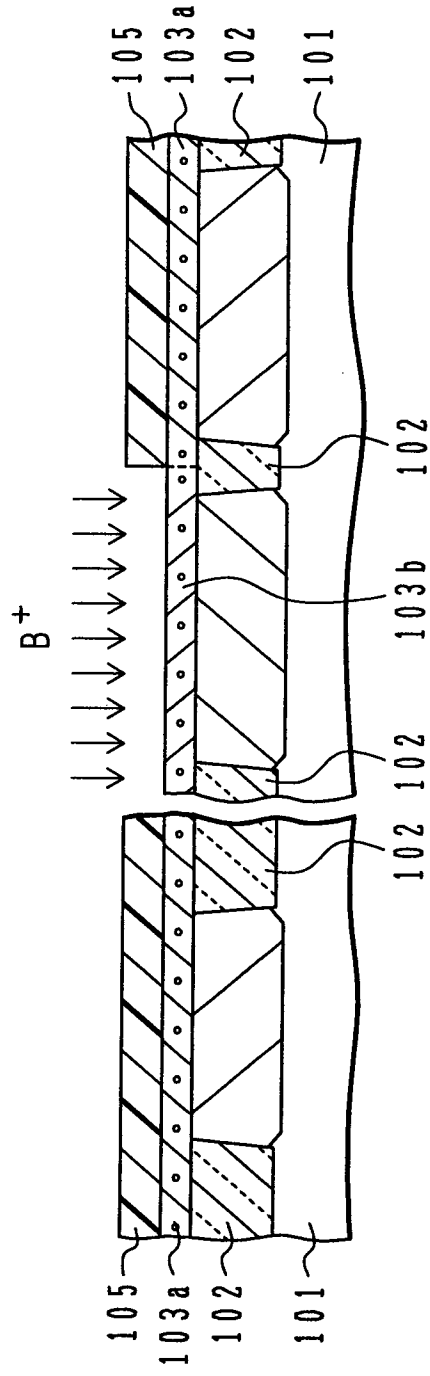


FIG.30B

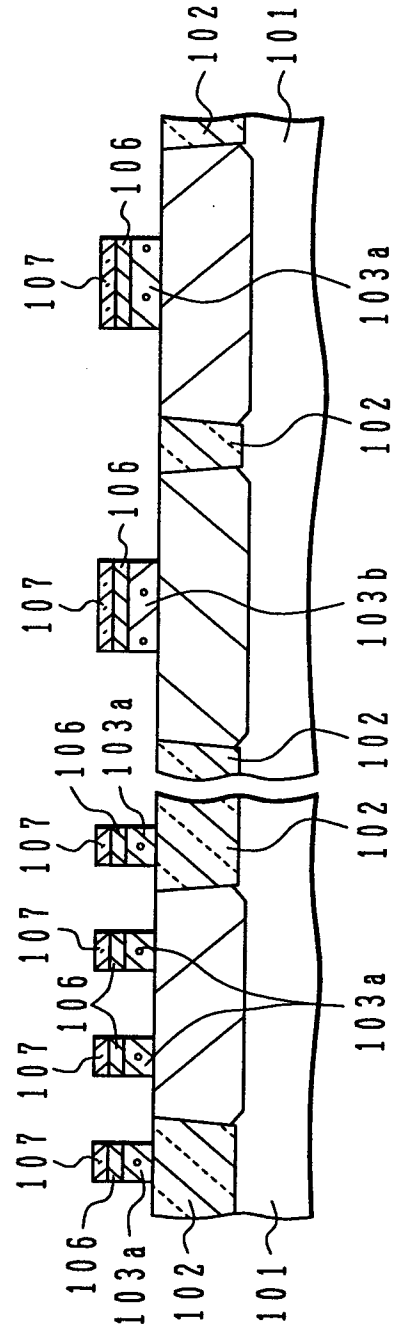


FIG.31A

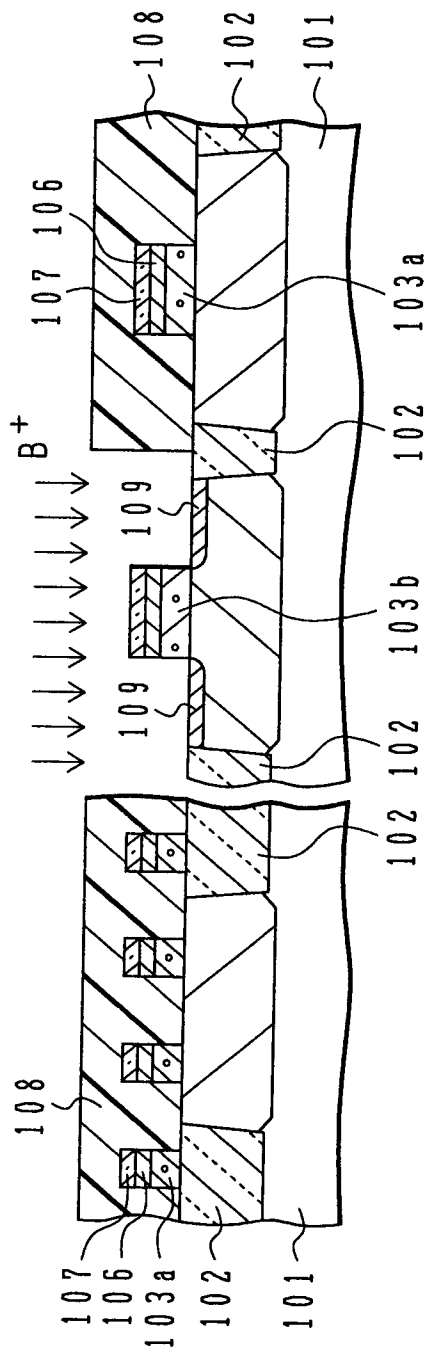


FIG.31B

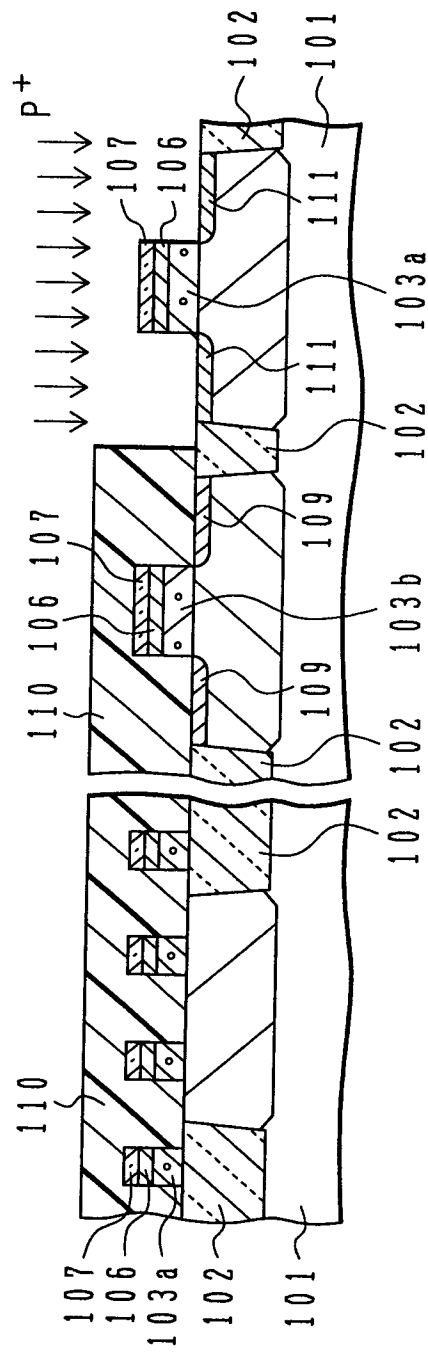


FIG. 32A

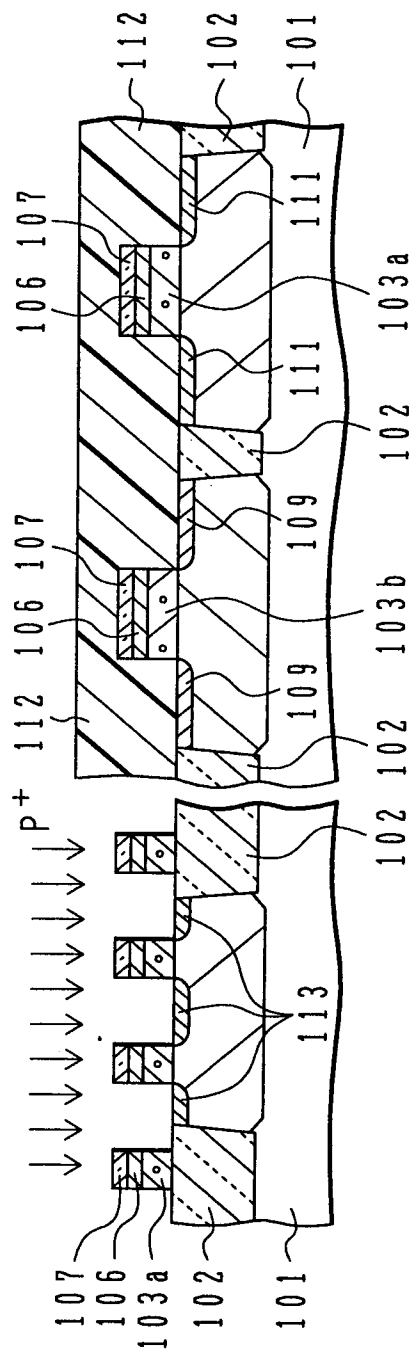


FIG. 32B

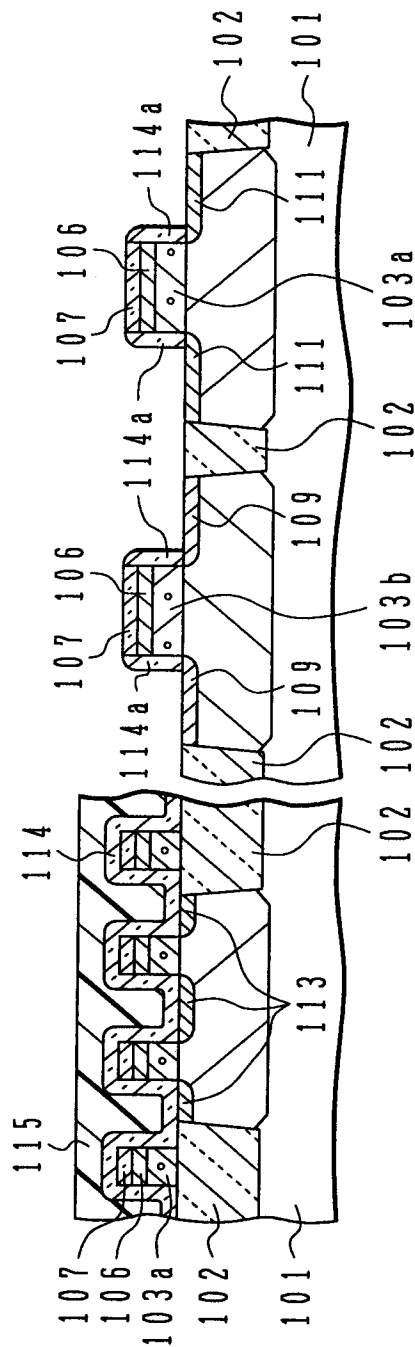


FIG.33

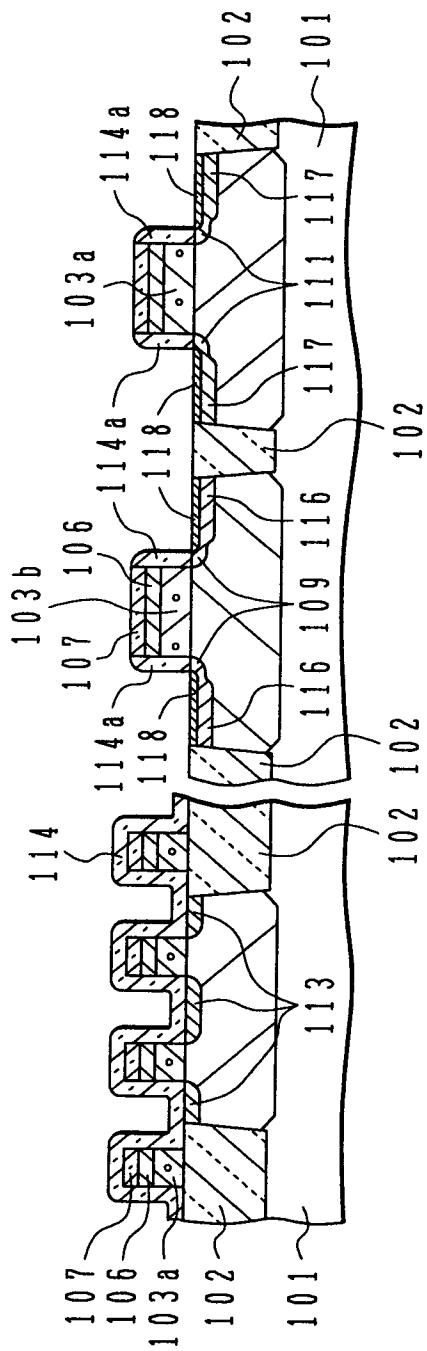


FIG.34

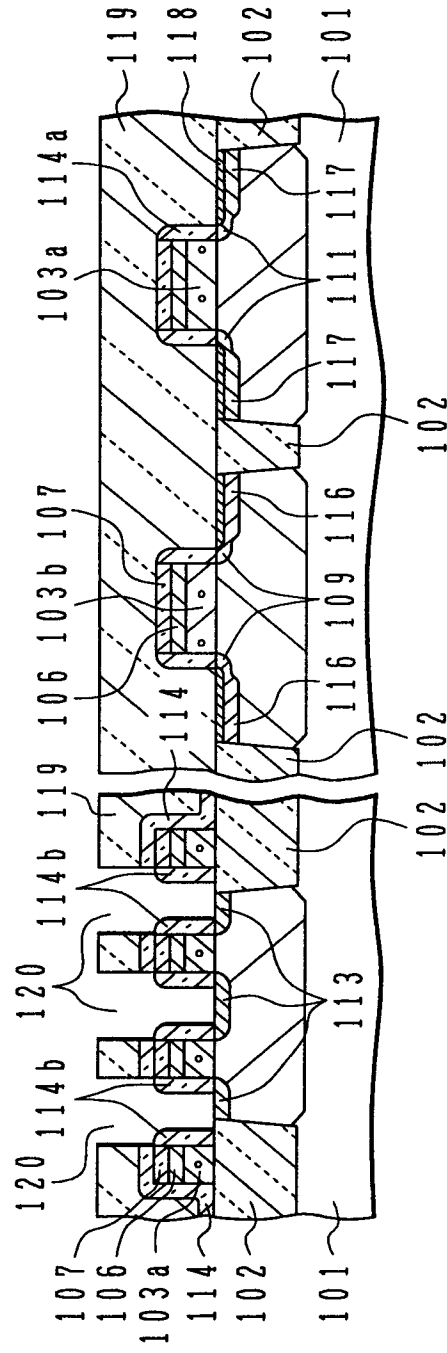


FIG.35

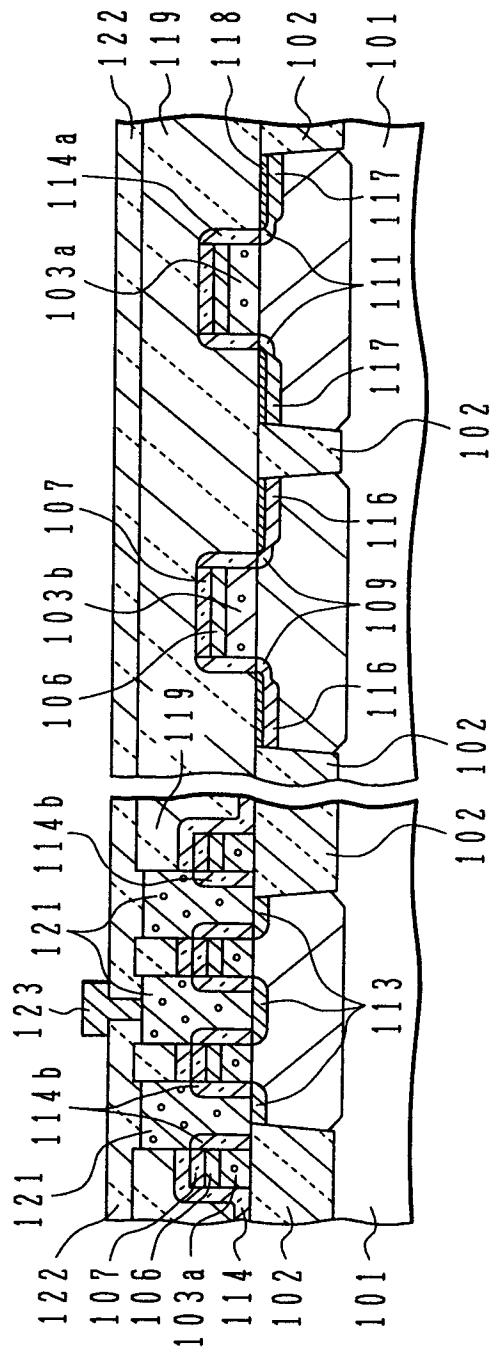


FIG.36

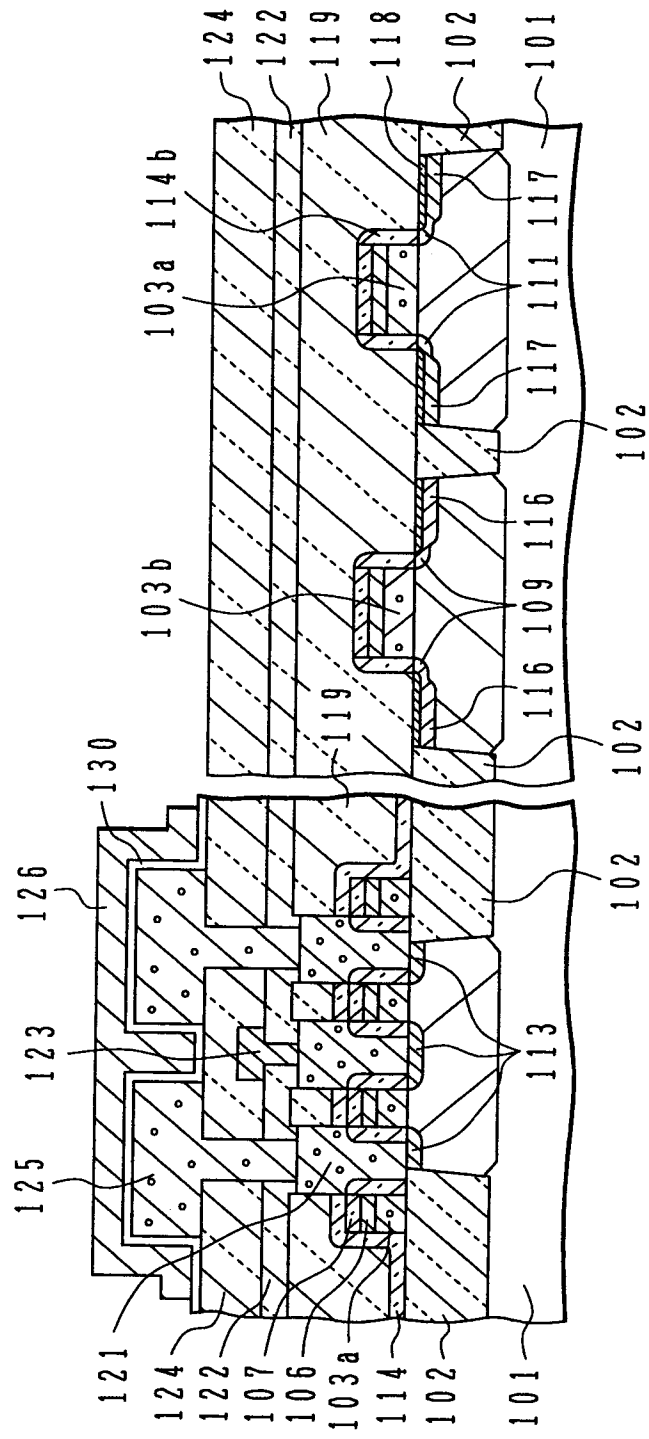


FIG.37

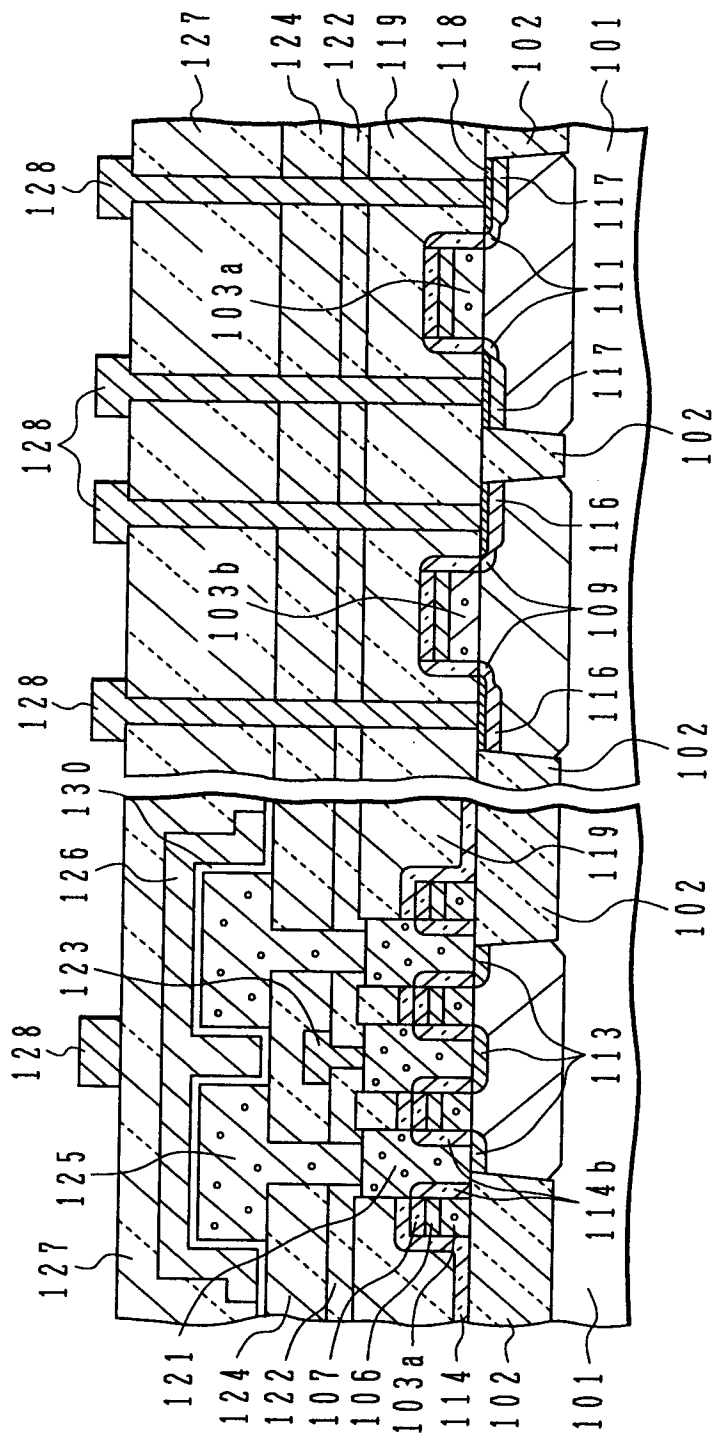


FIG.38

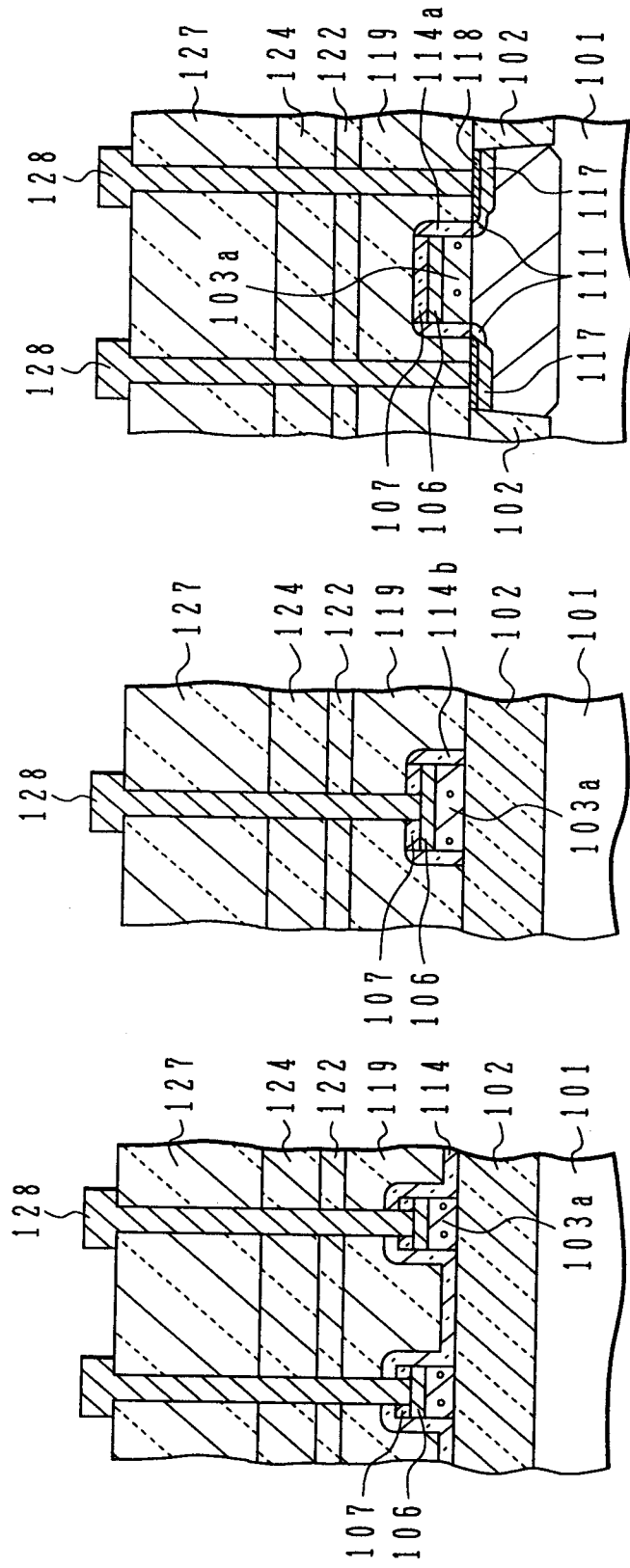


FIG.39A

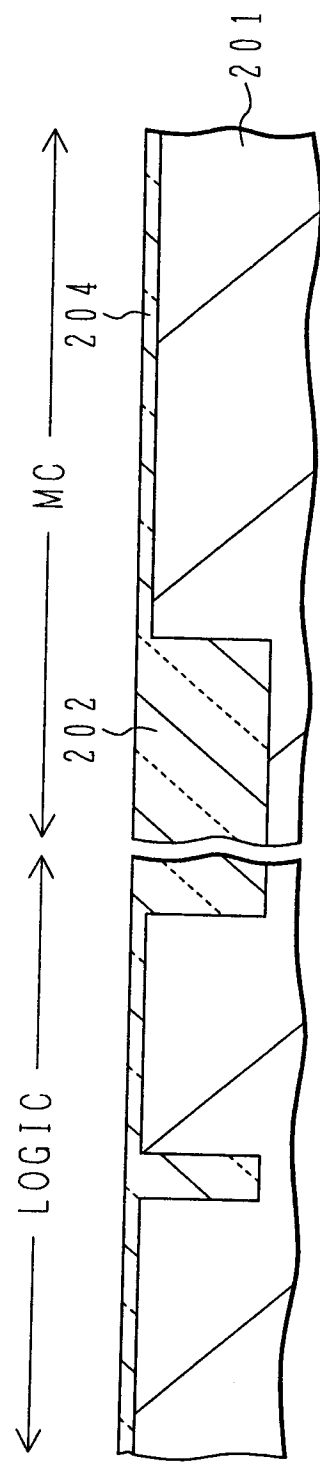


FIG.39B

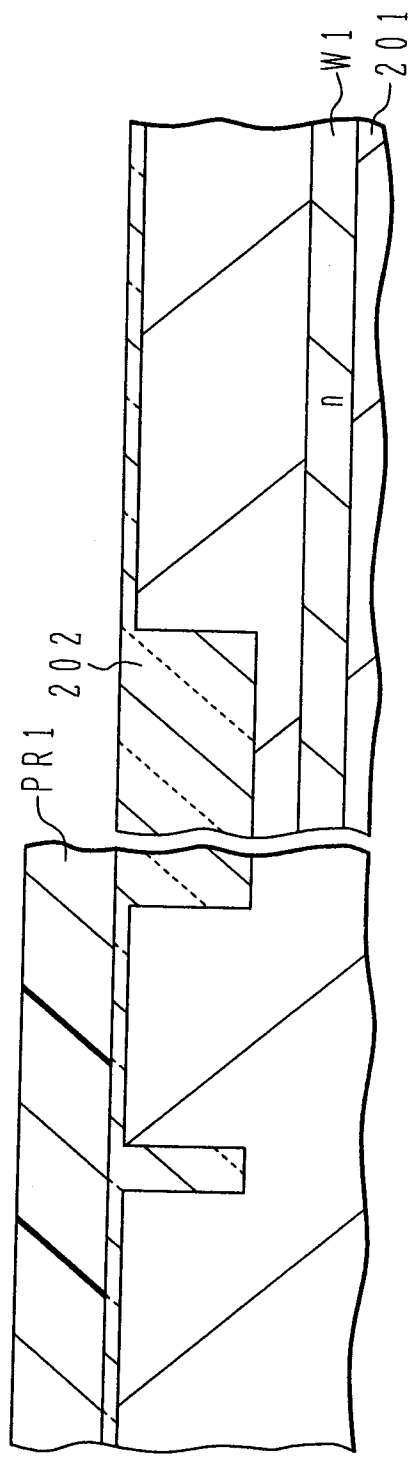


FIG.39C

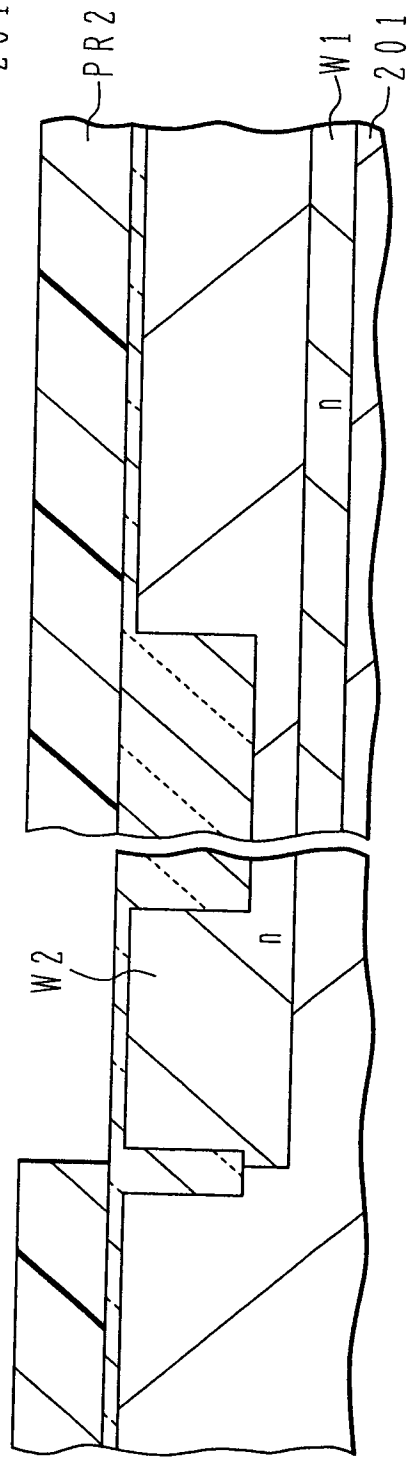


FIG. 40A

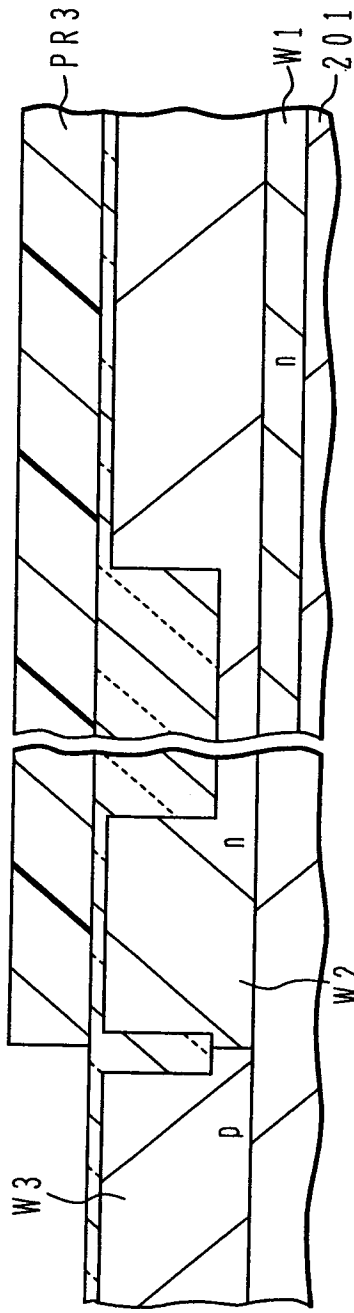


FIG. 40B

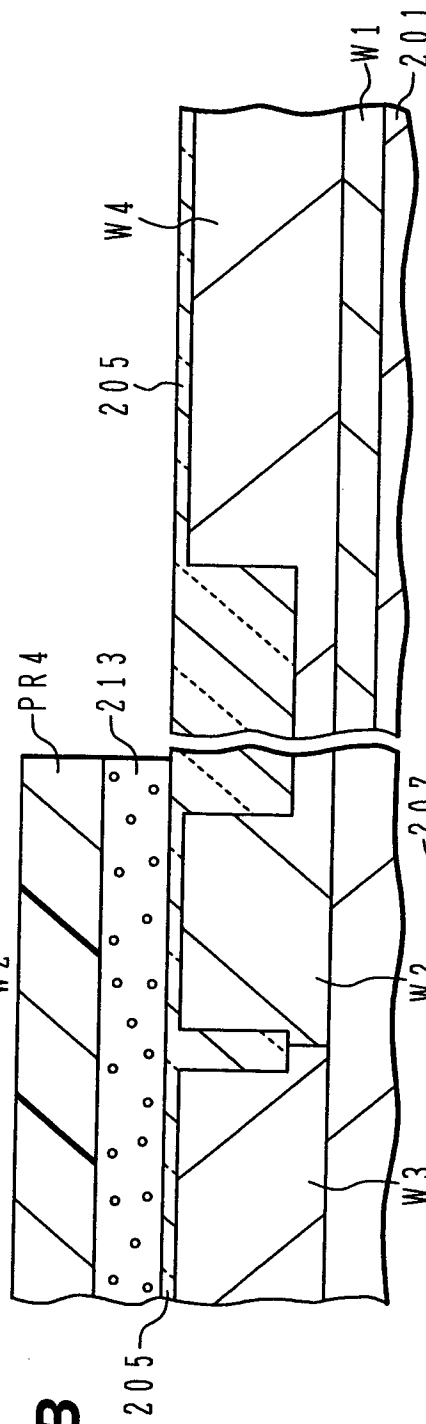


FIG. 40C

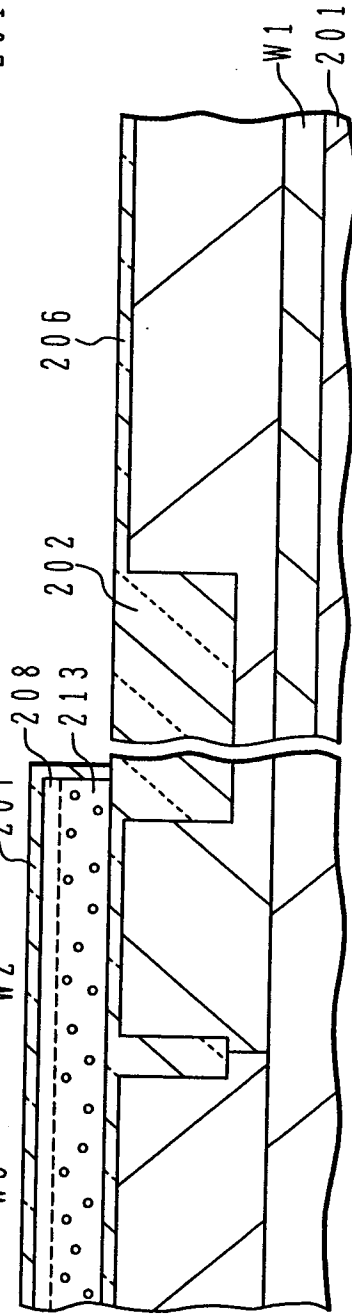


FIG.41A

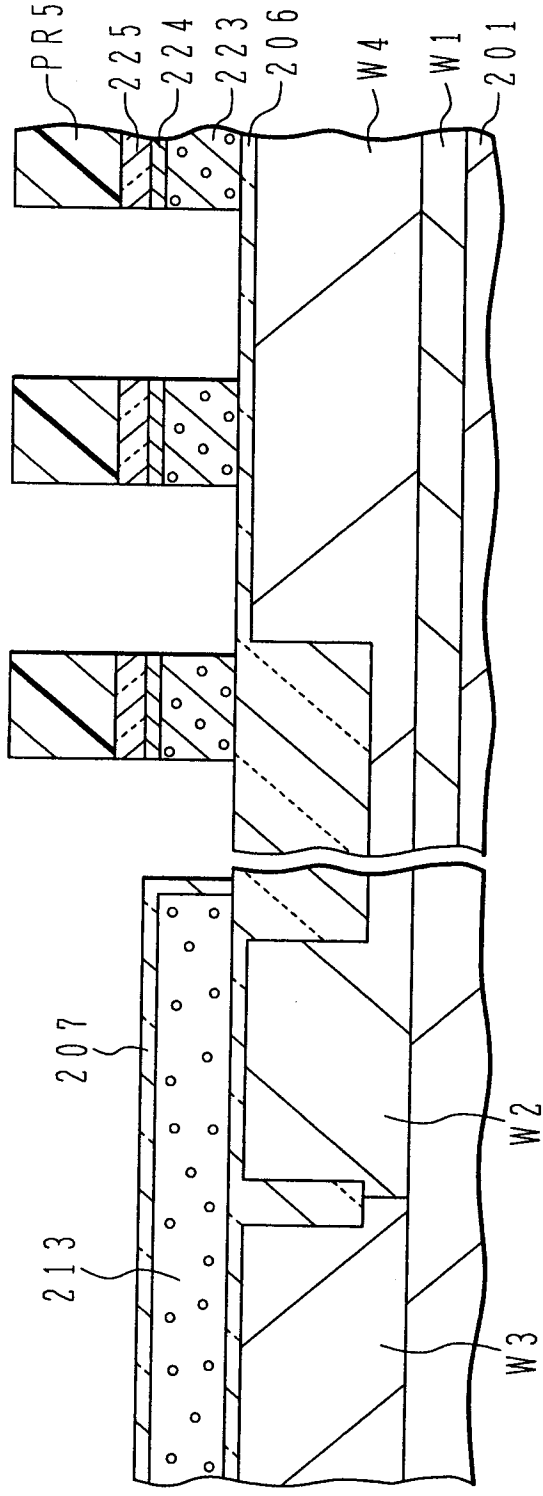
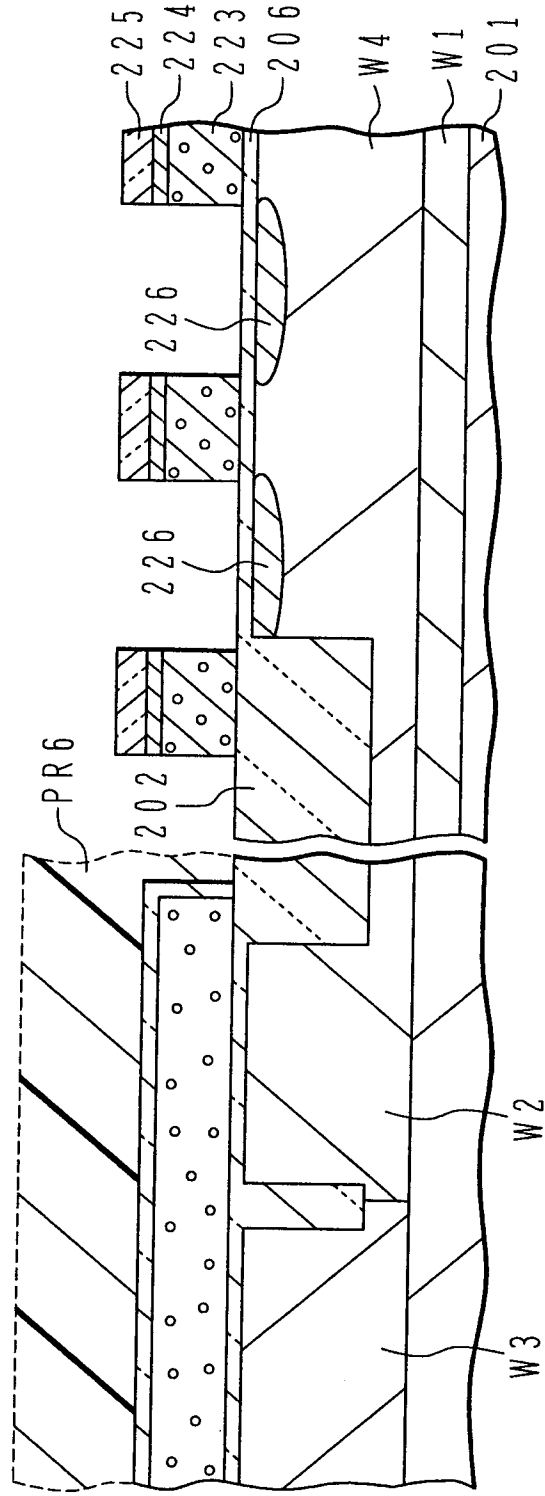


FIG.41B



[illegible][illegible]

FIG.45

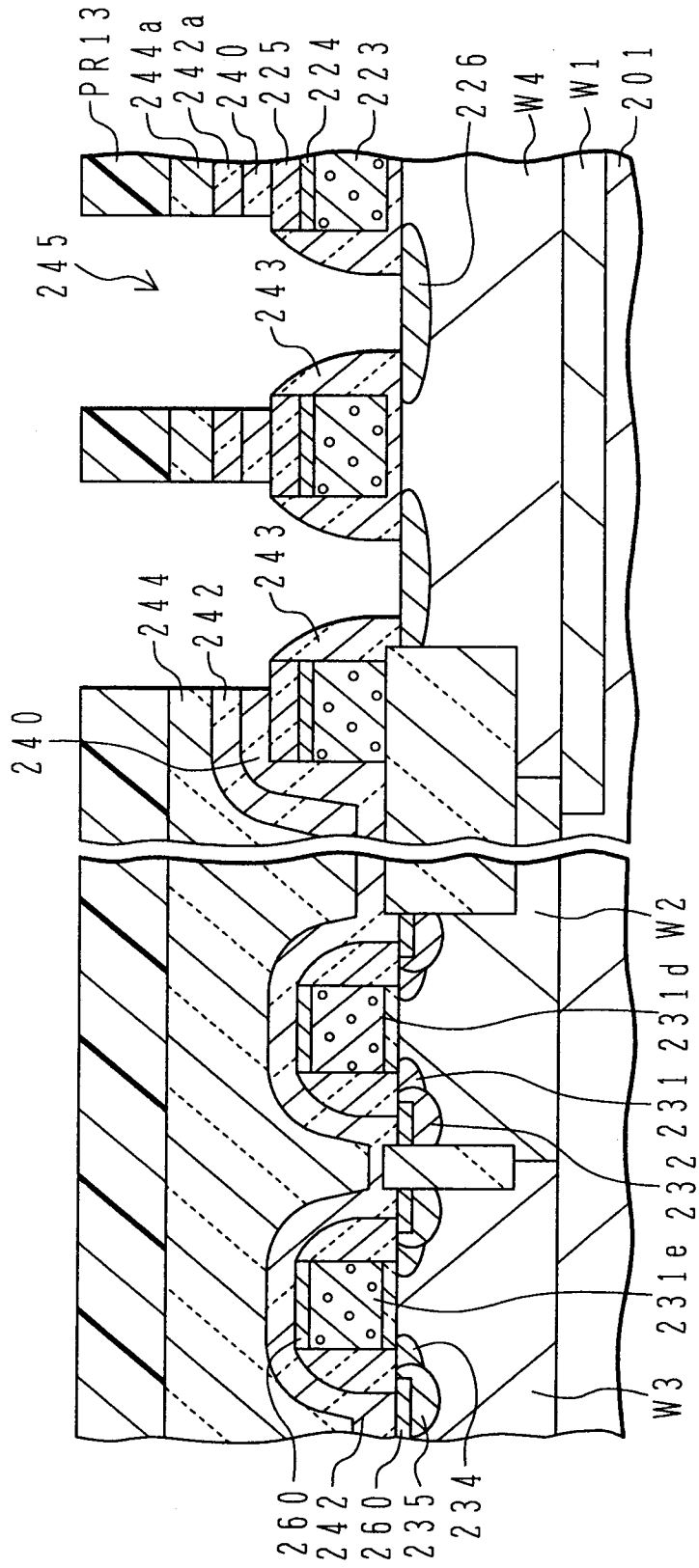


FIG. 46

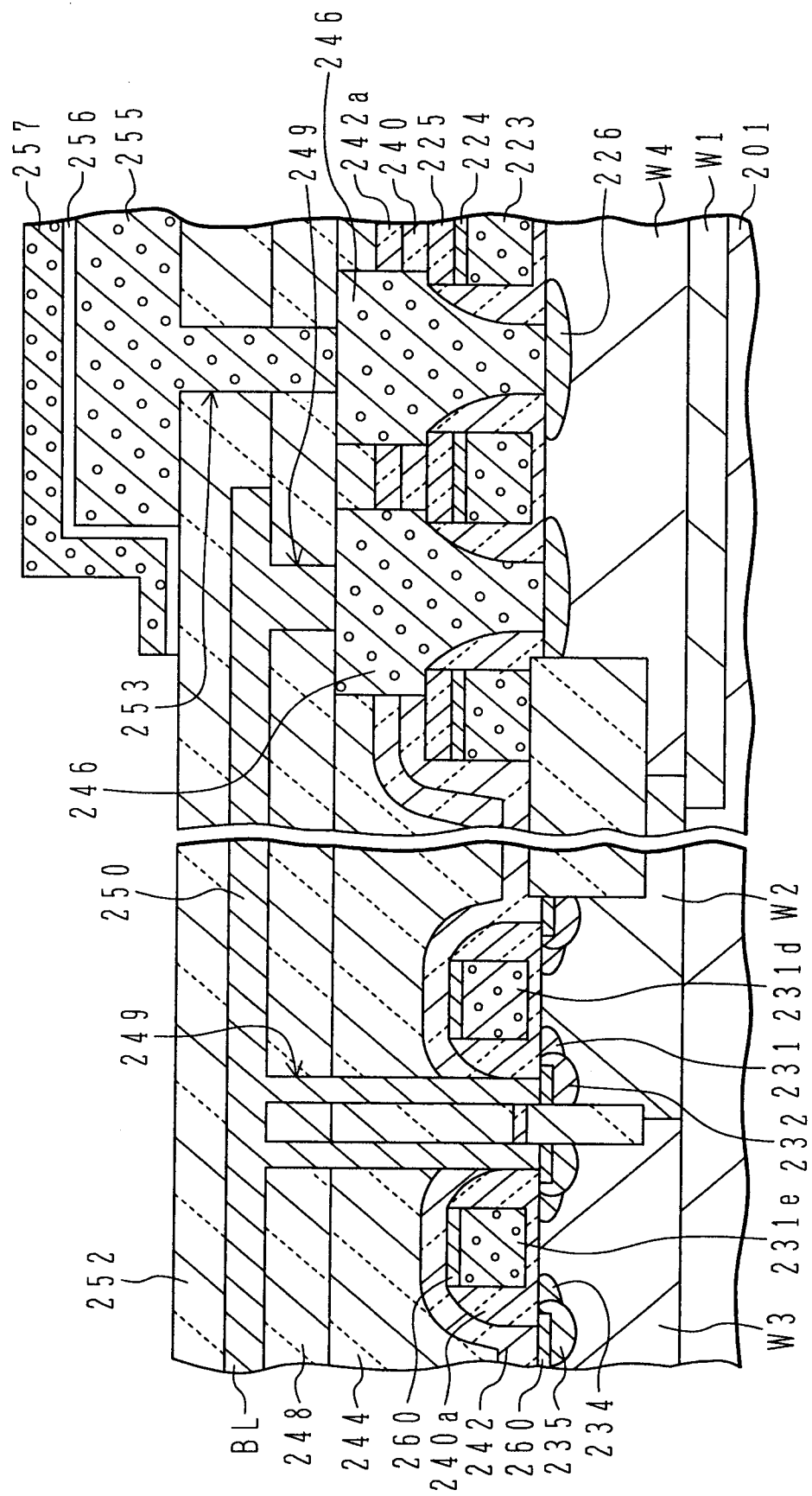


FIG.48

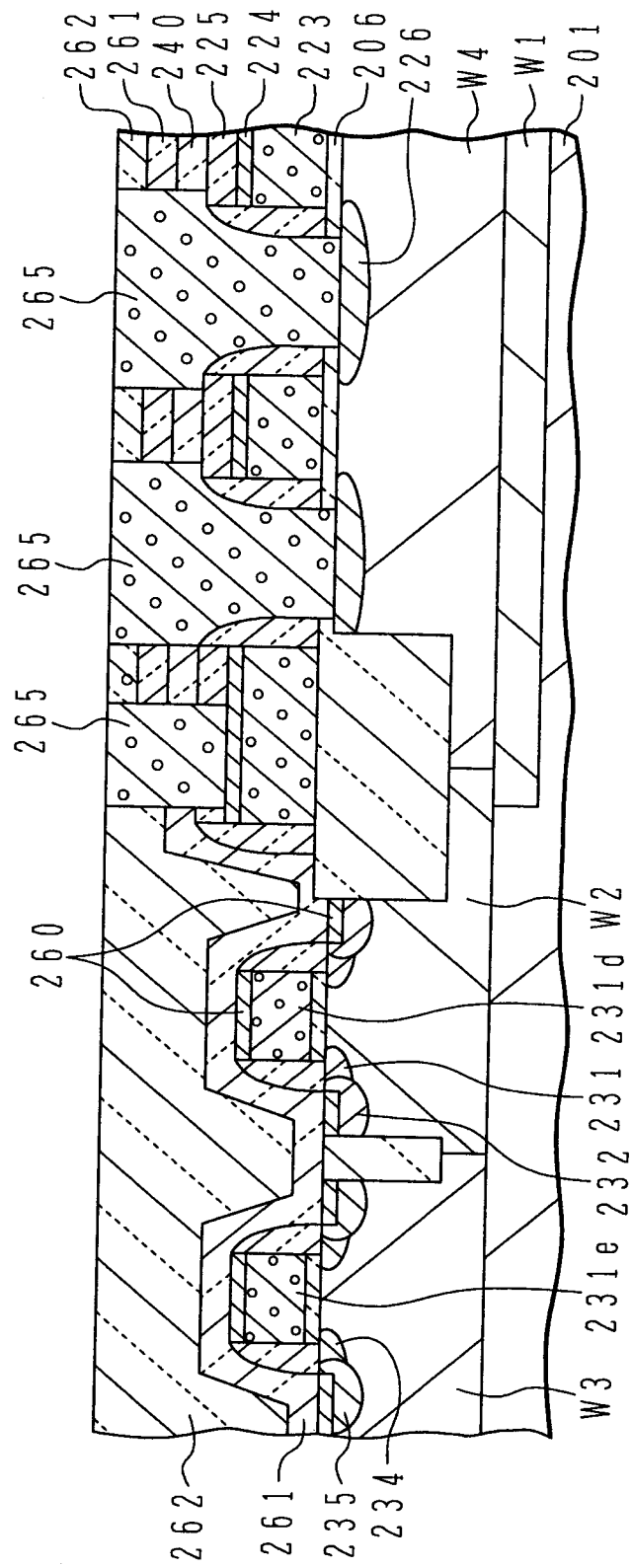
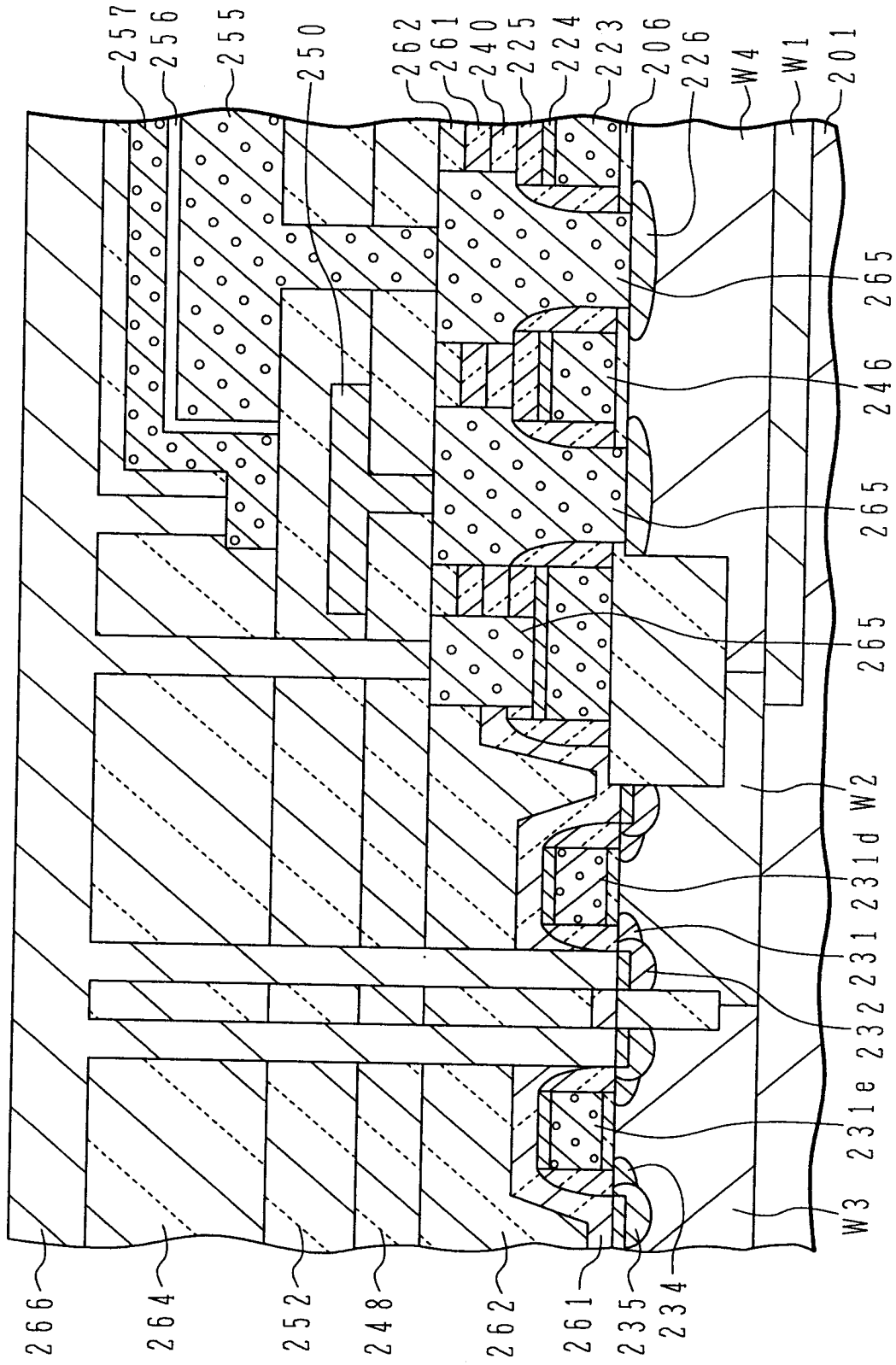


FIG. 49



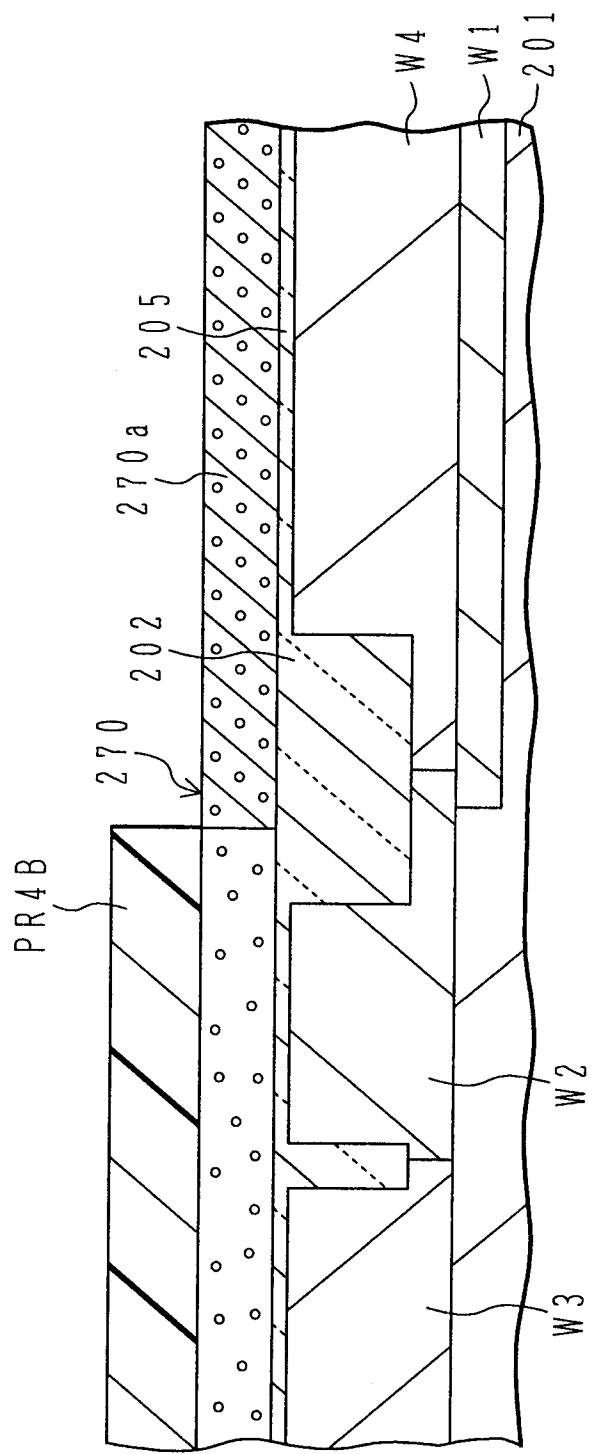


FIG. 50A

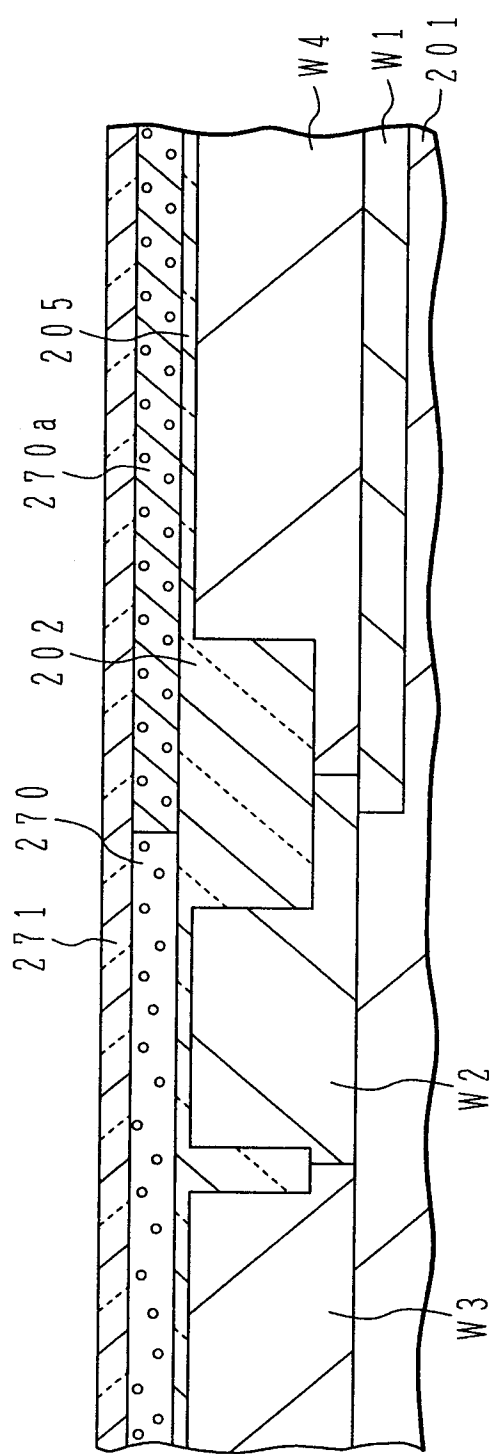


FIG. 50B

[illegible]

Fig. 1 is a cross-sectional view of a semiconductor device. The device includes a substrate 201. A layer 202 is formed on the substrate 201, and a top layer 205 is formed on the layer 202. The layer 202 has openings 270. A layer 271a is formed on the layer 202, and a layer 270 is formed on the layer 271a. The device is divided into regions W1, W2, W3, and W4. Labels PR6B and PR6BA are also present.

FIG. 52A

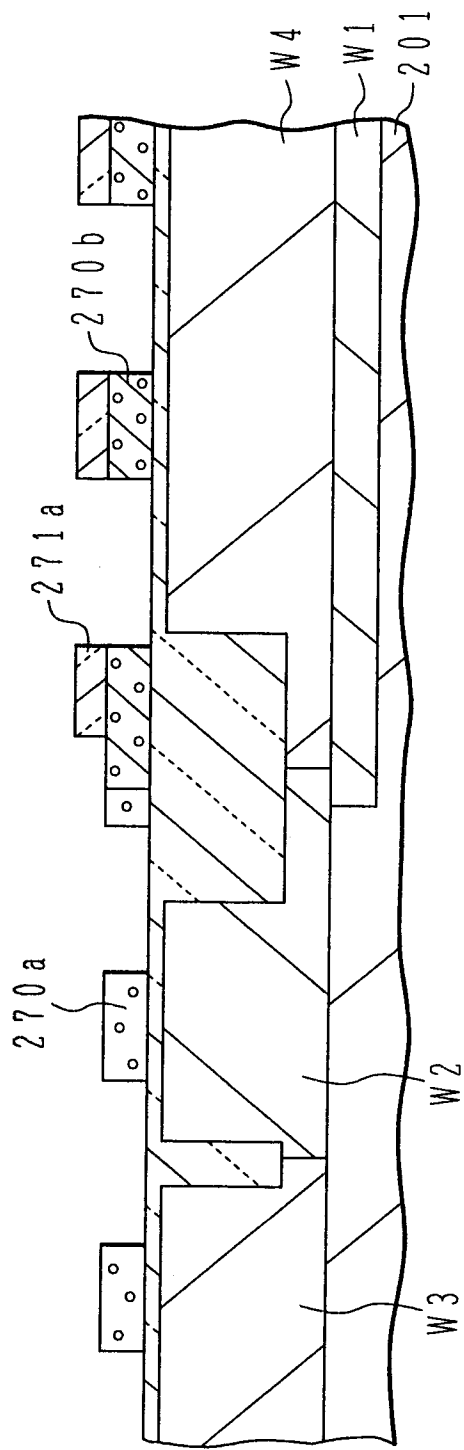


FIG. 52B

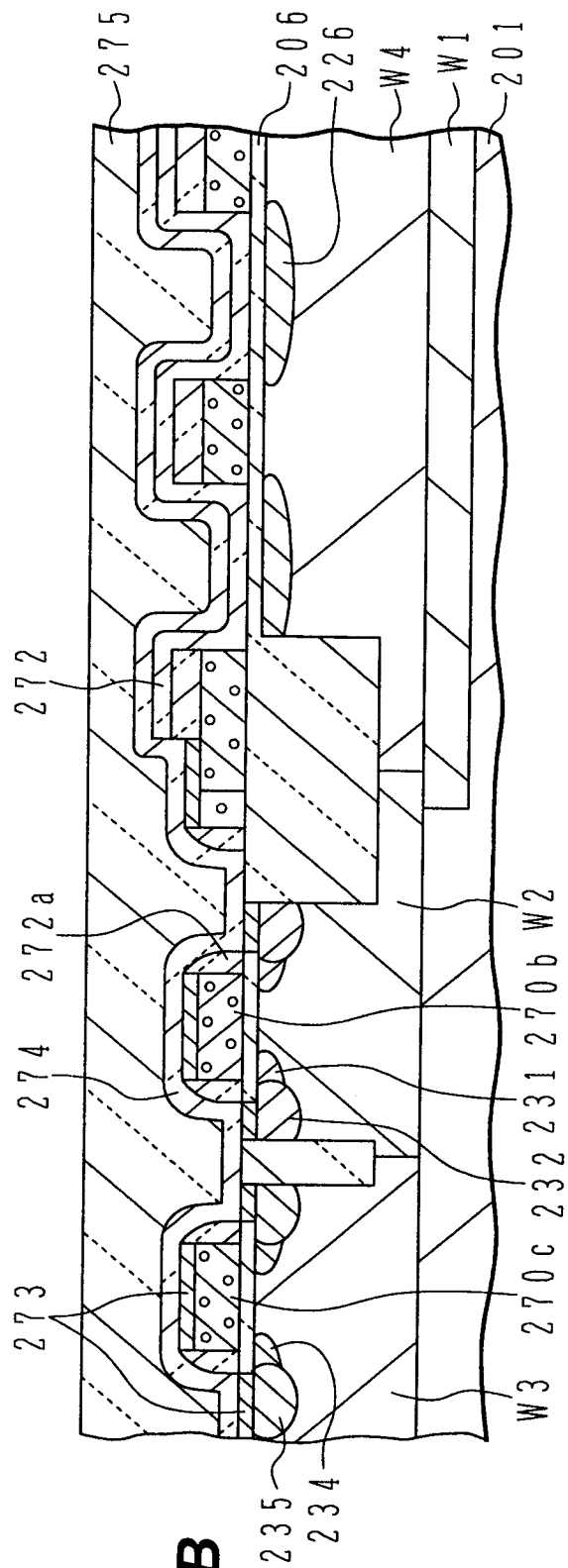


FIG.53

